CHAPTER 7

Thermal Management

7.1 Thermal Considerations

Thermal Considerations

7.1.1 Thermal Considerations for Power Semiconductors

The perfect power switch is not yet available. All power semiconductors dissipate power internally both during the on-state and during the transition between the on and off states. The amount of power dissipated internally generally speaking increases in line with the power being switched by the semiconductor. The capability of a switch to operate in a particular circuit will therefore depend upon the amount of power dissipated internally and the rise in the operating temperature of the silicon junction that this power dissipation causes. It is therefore important that circuit designers are familiar with the thermal characteristics of power semiconductors and are able to calculate power dissipation limits and junction operating temperatures.

This chapter is divided into two parts. Part One describes the essential thermal properties of semiconductors and explains the concept of a limit in terms of continuous mode and pulse mode operation. Part Two gives worked examples showing junction temperature calculations for a variety of applied power pulse waveforms.

PART ONE

The power dissipation limit

The maximum allowable power dissipation forms a limit to the safe operating area of power transistors. Power dissipation causes a rise in junction temperature which will, in turn, start chemical and metallurgical changes. The rate at which these changes proceed is exponentially related to temperature, and thus prolonged operation of a power transistor above its junction temperature rating is liable to result in reduced life. Operation of a device at, or below, its power dissipation rating (together with careful consideration of thermal resistances associated with the device) ensures that the junction temperature rating is not exceeded.

All power semiconductors have a power dissipation limitation. For rectifier products such as diodes, thyristors and triacs, the power dissipation rating can be easily translated in terms of current ratings; in the on-state the voltage drop is well defined. Transistors are, however, somewhat more complicated. A transistor, be it a power MOSFET or a bipolar, can operate in its on-state at any voltage up to its maximum rating depending on the circuit conditions. It is therefore necessary to specify a Safe Operating Area (SOA) for transistors which specifies the power dissipation limit in terms of a series of boundaries in the current and voltage plane. These operating areas are usually presented for mounting base temperatures of 25 ˚C. At higher temperatures, operating conditions must be checked to ensure that junction temperatures are not exceeding the desired operating level.

Continuous power dissipation

The total power dissipation in a semiconductor may be calculated from the product of the on-state voltage and the forward conduction current. The heat dissipated in the junction of the device flows through the thermal resistance between the junction and the mounting base, R_{thj-mb}. The thermal equivalent circuit of Fig. 1 illustrates this heat flow; P_{tot} can be regarded as a thermal current, and the temperature difference between the junction and mounting base ΔT_{j-mb} as a thermal voltage. By analogy with Ohm's law, it follows that:

$$P_{tot} = \frac{T_j - T_{mb}}{R_{thj-mb}} \qquad 1$$

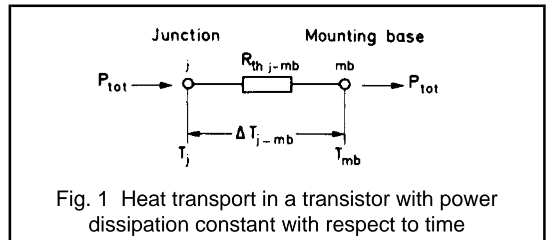

Fig. 1 Heat transport in a transistor with power dissipation constant with respect to time

Fig. 2 shows the dependence of the maximum power dissipation on the temperature of the mounting base. P_{totmax} is limited either by a maximum temperature difference:

$$\Delta T_{j-mb\,\max} = T_{jmax} - T_{mb\,K} \qquad 2$$

or by the maximum junction temperature T_{jmax} ($T_{mb\,K}$ is usually 25˚C and is the value of T_{mb} above which the maximum power dissipation must be reduced to maintain the operating point within the safe operating area).

In the first case, $T_{mb} \leq T_{mb\,K}$:

$$P_{tot\,\max K} = \frac{\Delta T_{j-mb\,\max}}{R_{thj-mb}}; \qquad 3$$

that is, the power dissipation has a fixed limit value ($P_{tot\,max\,K}$ is the maximum d.c. power dissipation *below* $T_{mb\,K}$). If the transistor is subjected to a mounting-base temperature $T_{mb\,1}$, its junction temperature will be less than T_{jmax} by an amount (T_{mbK} - $T_{mb\,1}$), as shown by the broken line in Fig. 2.

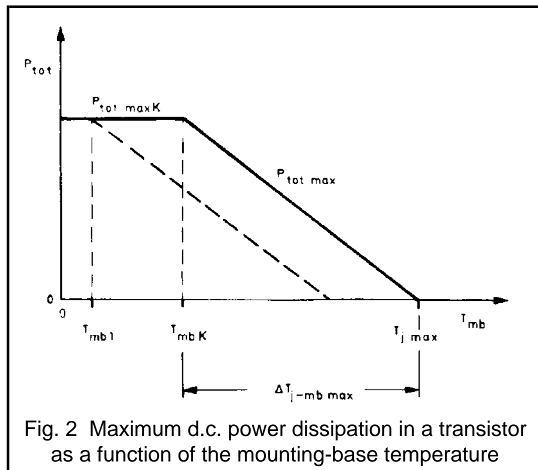

Fig. 2 Maximum d.c. power dissipation in a transistor as a function of the mounting-base temperature

In the second case, $T_{mb} > T_{mb\,K}$:

$$P_{tot\,\max} = \frac{T_{jmax} - T_{mb}}{R_{thj-mb}}; \qquad 4$$

that is, the power dissipation must be reduced as the mounting base temperature increases along the sloping straight line in Fig. 2. Equation 4 shows that the lower the thermal resistance $R_{thj\text{-}mb}$, the steeper is the slope of the line. In this case, T_{mb} is the maximum mounting-base temperature that can occur in operation.

Example

The following data is provided for a particular transistor.

$P_{tot\,maxK}$ = 75 W

T_{jmax} = 175 ˚C

$R_{thj\text{-}mb}$ ≤ 2 K/W

The maximum permissible power dissipation for continuous operation at a maximum mounting-base temperature of T_{mb} = 80 ˚C is required.

Note that the maximum value of T_{mb} is chosen to be significantly higher than the maximum ambient temperature to prevent an excessively large heatsink being required.

From Eq. 4 we obtain:

$$P_{tot\,\max} = \frac{175 - 80}{2} W, \quad = 47.5\,W$$

Provided that the transistor is operated within SOA limits, this value is permissible since it is below $P_{tot\,max\,K}$. The same result can be obtained graphically from the $P_{tot\,max}$ diagram (Fig. 3) for the relevant transistor.

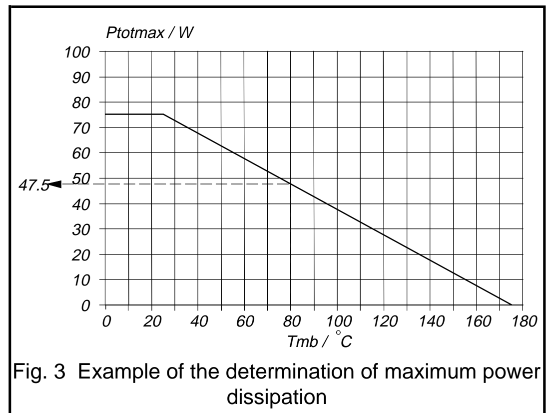

Fig. 3 Example of the determination of maximum power dissipation

Pulse power operation

When a power transistor is subjected to a pulsed load, higher peak power dissipation is permitted. The materials in a power transistor have a definite thermal capacity, and thus the critical junction temperature will not be reached instantaneously, even when excessive power is being dissipated in the device. The power dissipation limit may be extended for intermittent operation. The size of the extension will depend on the duration of the operation period (that is, pulse duration) and the frequency with which operation occurs (that is, duty factor).

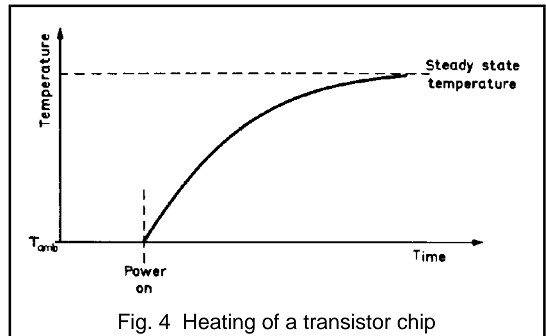

Fig. 4 Heating of a transistor chip

If power is applied to a transistor, the device will immediately start to warm up (Fig. 4). If the power dissipation continues, a balance will be struck between heat generation and removal resulting in the stabilisation of T_j and $\Delta T_{j\text{-}mb}$. Some heat energy will be stored by the thermal capacity of the device, and the stable conditions will be determined by the thermal resistances associated with the transistor and its thermal environment. When the power dissipation ceases, the device will cool (the heating and cooling laws will be identical, see Fig. 5). However, if the power dissipation ceases before the temperature of the transistor stabilises, the peak values of T_j and $\Delta T_{j\text{-}mb}$ will be less than the values

reached for the same level of continuous power dissipation (Fig. 6). If the second pulse is identical to the first, the peak temperature attained by the device at the end of the second pulse will be greater than that at the end of the first pulse. Further pulses will build up the temperature until some new stable situation is attained (Fig. 7). The temperature of the device in this stable condition will fluctuate above and below the mean. If the upward excursions extend into the region of excessive T_j then the life expectancy of the device may be reduced. This can happen with high-power low-duty-factor pulses, even though the *average* power is below the d.c. rating of the device.

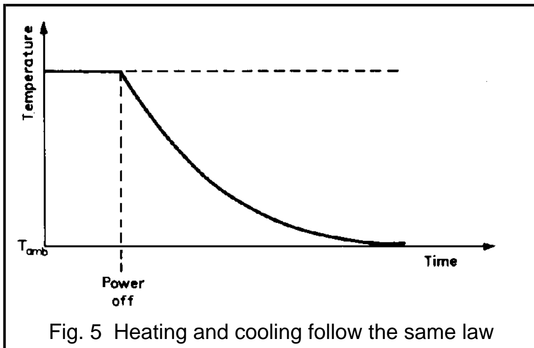

Fig. 5 Heating and cooling follow the same law

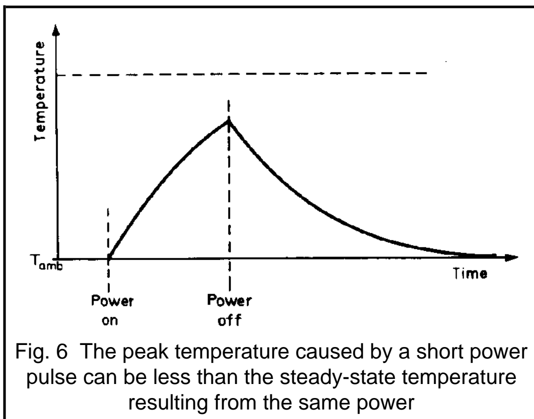

Fig. 6 The peak temperature caused by a short power pulse can be less than the steady-state temperature resulting from the same power

Fig. 8 shows a typical safe operating area for d.c. operation of a power MOSFET. The corresponding rectangular-pulse operating areas with a fixed duty factor, δ = 0, and the pulse time t_p as a parameter, are also shown. These boundaries represent the largest possible extension of the operating area for particular pulse times. When the pulse time becomes very short, the power dissipation does not have a limiting action and the pulse current and maximum voltage form the only limits. This rectangle represents the largest possible pulse operating area.

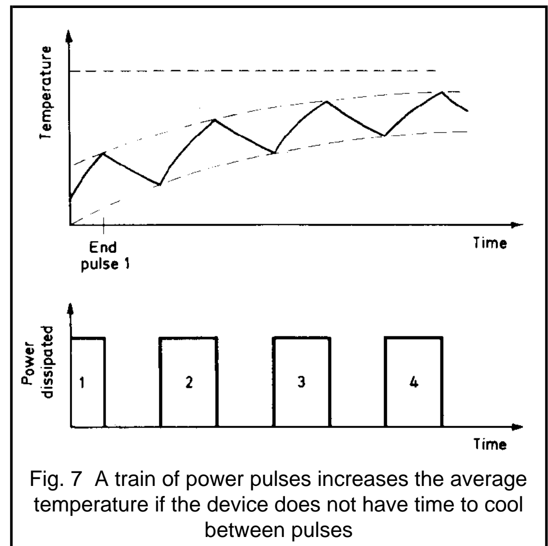

Fig. 7 A train of power pulses increases the average temperature if the device does not have time to cool between pulses

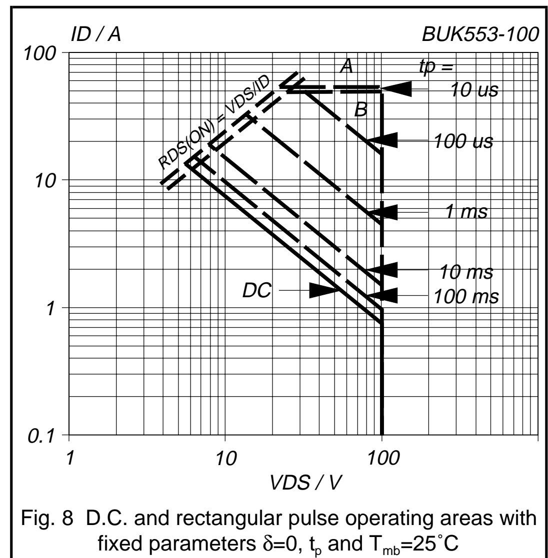

Fig. 8 D.C. and rectangular pulse operating areas with fixed parameters δ=0, t_p and T_{mb}=25˚C

In general, the shorter the pulse and the lower the frequency, the lower the temperature that the junction reaches. By analogy with Eq. 3, it follows that:

$$P_{tot\,M} = \frac{T_j - T_{mb}}{Z_{thj-mb}}, \qquad 5$$

where $Z_{thj\text{-}mb}$ is the transient thermal impedance between the junction and mounting base of the device. It depends on the pulse duration t_p, and the duty factor δ, where:

$$\delta = \frac{t_p}{T}, \qquad 6$$

and T is the pulse period. Fig. 9 shows a typical family of curves for thermal impedance against pulse duration, with duty factor as a parameter.

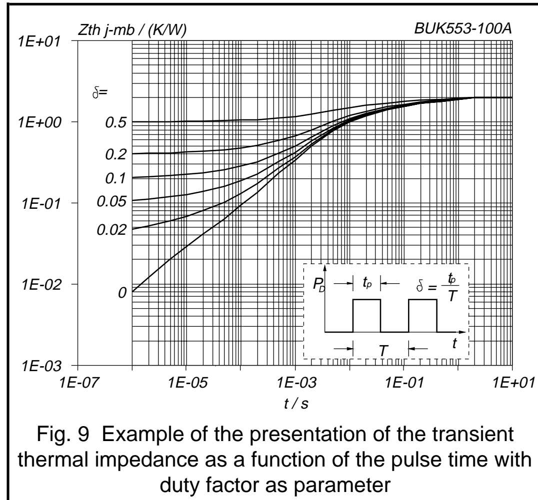

Fig. 9 Example of the presentation of the transient thermal impedance as a function of the pulse time with duty factor as parameter

Again, the maximum pulse power dissipation is limited either by the maximum temperature difference $\Delta T_{j\text{-}mb\,max}$ (Eq. 2), or by the maximum junction temperature T_{jmax}, and so by analogy with Eqs. 3 and 4:

$$P_{tot\,\max K} = \frac{\Delta T_{j-mb\,\max}}{Z_{thj-mb}}, \qquad 7$$

when $T_{mb} \leq T_{mb\,K}$, and:

$$P_{tot\,M\,\max} = \frac{T_{jmax} - T_{mb}}{Z_{thj-mb}}, \qquad 8$$

when $T_{mb} > T_{mb\,K}$. That is, below a mounting-base temperature of $T_{mb\,K}$, the maximum power dissipation has a fixed limit value; and above $T_{mb\,K}$, the power dissipation must be reduced linearly with increasing mounting-base temperature.

Short pulse duration (Fig. 10a)

As the pulse duration becomes very short, the fluctuations of junction temperature become negligible, owing to the internal thermal capacity of the transistor. Consequently, the only factor to be considered is the heating of the junction by the average power dissipation; that is:

$$P_{tot(av)} = \delta P_{tot\,M} \qquad 9$$

The transient thermal impedance becomes:

$$\lim_{t_p \to 0} Z_{thj-mb} = \delta R_{thj-mb} \qquad 10$$

The $Z_{thj\text{-}mb}$ curves approach this value asymptotically as t_p decreases. Fig. 9 shows that, for duty factors in the range 0.1 to 0.5, the limit values given by Eq. 10 have virtually been reached at $t_p = 10^{-6}$ s.

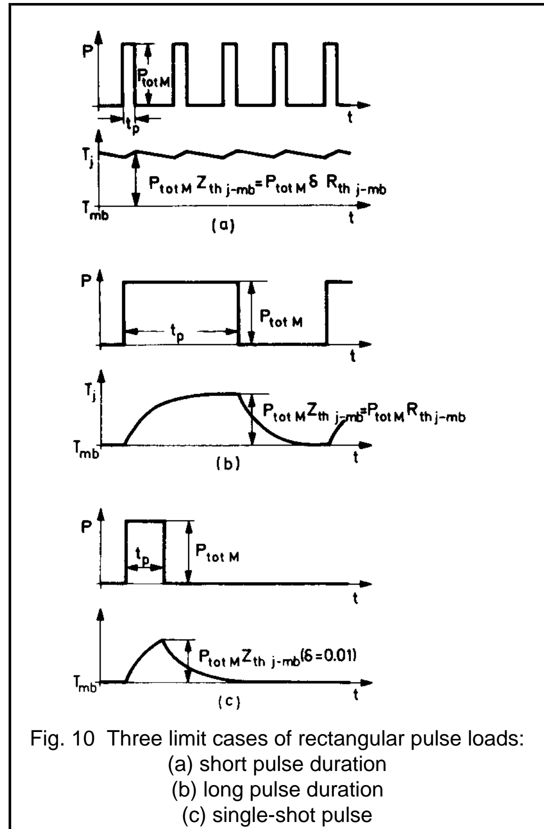

Fig. 10 Three limit cases of rectangular pulse loads:
(a) short pulse duration
(b) long pulse duration
(c) single-shot pulse

Long pulse duration (Fig. 10b)

As the pulse duration increases, the junction temperature approaches a stationary value towards the end of a pulse. The transient thermal impedance tends to the thermal resistance for continuous power dissipation; that is:

$$\lim_{t_p \to \infty} Z_{thj-mb} = R_{thj-mb} \qquad 11$$

Fig. 9 shows that $Z_{thj\text{-}mb}$ approaches this value as t_p becomes large. In general, transient thermal effects die out in most power transistors within 0.1 to 1.0 seconds. This time depends on the material and construction of the case, the size of the chip, the way it is mounted, and other factors. Power pulses with a duration in excess of this time have approximately the same effect as a continuous load.

Single-shot pulses (Fig. 10c)

As the duty factor becomes very small, the junction tends to cool down completely between pulses so that each pulse can be treated individually. When considering single pulses, the Z_{thj-mb} values for $\delta = 0$ (Fig. 9) give sufficiently accurate results.

PART TWO

Calculating junction temperatures

Most applications which include power semiconductors usually involve some form of pulse mode operation. This section gives several worked examples showing how junction temperatures can be simply calculated. Examples are given for a variety of waveforms:

(1) Periodic Waveforms

(2) Single Shot Waveforms

(3) Composite Waveforms

(4) A Pulse Burst

(5) Non Rectangular Pulses

From the point of view of reliability it is most important to know what the peak junction temperature will be when the power waveform is applied and also what the average junction temperature is going to be.

Peak junction temperature will usually occur at the end of an applied pulse and its calculation will involve transient thermal impedance. The average junction temperature (where applicable) is calculated by working out the average power dissipation using the d.c. thermal resistance.

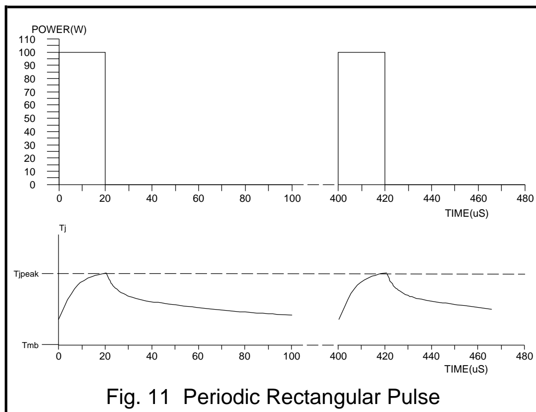

Fig. 11 Periodic Rectangular Pulse

When considering the junction temperature in a device, the following formula is used:

$$T_j = T_{mb} + \Delta T_{j-mb} \quad (14)$$

where $\Delta T_{j\text{-}mb}$ is found from a rearrangement of equation 7. In all the following examples the mounting base temperature (T_{mb}) is assumed to be 75˚C.

Periodic rectangular pulse

Fig. 11 shows an example of a periodic rectangular pulse. This type of pulse is commonly found in switching applications. 100W is dissipated every 400µs for a period of 20µs, representing a duty cycle (δ) of 0.05. The peak junction temperature is calculated as follows:

Peak T_j:

$$t = 2 \times 10^{-5}\text{s}$$

$$P = 100\text{W}$$

$$\delta = \frac{20}{400} = 0.05$$

$$Z_{thj-mb} = 0.12\text{K/W}$$

$$\Delta T_{j-mb} = P \times Z_{thj-mb} = 100 \times 0.12 = 12°\text{C}$$

$$T_j = T_{mb} + \Delta T_{j-mb} = 75 + 12 = 87°\text{C}$$

Average T_j:

$$P_{av} = P \times \delta = 100 \times 0.05 = 5\text{W}$$

$$\Delta T_{j-mb(av)} = P_{av} \times Z_{thj-mb(\delta=1)} = 5 \times 2 = 10°\text{C}$$

$$T_{j(av)} = T_{mb} + \Delta T_{j-mb(av)} = 75 + 10 = 85°\text{C}$$

The value for $Z_{th\,j\text{-}mb}$ is taken from the δ=0.05 curve shown in Fig. 12 (This diagram repeats Fig. 9 but has been simplified for clarity). The above calculation shows that the peak junction temperature will be 85˚C.

Single shot rectangular pulse

Fig. 13 shows an example of a single shot rectangular pulse. The pulse used is the same as in the previous example, which should highlight the differences between periodic and single shot thermal calculations. For a single shot pulse, the time period between pulses is infinity, ie the duty cycle δ=0. In this example 100W is dissipated for a period of 20µs. To work out the peak junction temperature the following steps are used:

$$t = 2 \times 10^{-5}\text{s}$$

$$P = 100\text{W}$$

$$\delta = 0$$

$$Z_{thj-mb} = 0.04\text{K/W}$$

$$\Delta T_{j-mb} = P \times Z_{thj-mb} = 100 \times 0.04 = 4°\text{C}$$

The value for $Z_{th\,j\text{-}mb}$ is taken from the δ=0 curve shown in Fig. 12. The above calculation shows that the peak junction temperature will be 4˚C above the mounting base temperature.

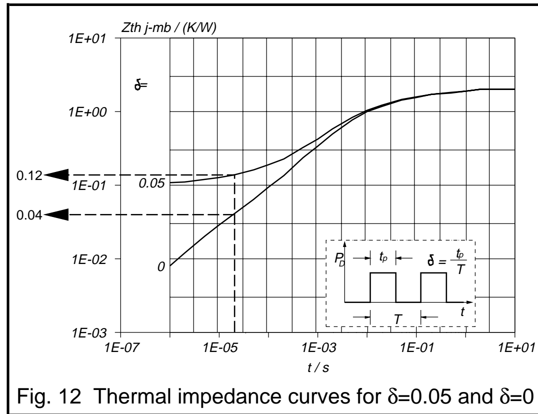

Fig. 12 Thermal impedance curves for δ=0.05 and δ=0

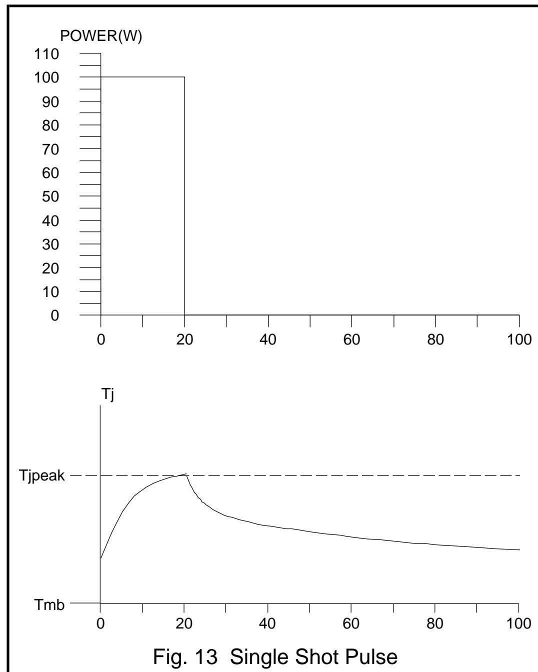

Fig. 13 Single Shot Pulse

For a single shot pulse, the average power dissipated and average junction temperature are not relevant.

Composite rectangular pulse

In practice, a power device frequently has to handle composite waveforms, rather than the simple rectangular pulses shown so far. This type of signal can be simulated by superimposing several rectangular pulses which have a common period, but both positive and negative amplitudes, in addition to suitable values of t_p and δ.

By way of an example, consider the composite waveform shown in Fig. 14. To show the way in which the method used for periodic rectangular pulses is extended to cover composite waveforms, the waveform shown has been chosen to be an extension of the periodic rectangular pulse example. The period is 400µs, and the waveform consists of three rectangular pulses, namely 40W for 10µs, 20W for 150µs and 100W for 20µs. The peak junction temperature may be calculated at any point in the cycle. To be able to add the various effects of the pulses at this time, all the pulses, both positive and negative, must end at time t_x in the first calculation and t_y in the second calculation. Positive pulses increase the junction temperature, while negative pulses decrease it.

Calculation for time t_x

$$\Delta T_{j-mb@x} = P_1.Z_{thj-mb(t1)} + P_2.Z_{thj-mb(t3)} + P_3.Z_{thj-mb(t4)} - P_1.Z_{thj-mb(t2)} - P_2.Z_{thj-mb(t4)} \qquad 15$$

In equation 15, the values for P_1, P_2 and P_3 are known: P_1=40W, P_2=20W and P_3=100W. The Z_{th} values are taken from Fig. 9. For each term in the equation, the equivalent duty cycle must be worked out. For instance the first superimposed pulse in Fig. 14 lasts for a time t1 = 180µs, representing a duty cycle of 180/400 = 0.45 = δ. These values can then be used in conjunction with Fig. 9 to find a value for Z_{th}, which in this case is 0.9K/W. Table 1a gives the values calculated for this example.

		t1 180µs	t2 170µs	t3 150µs	t4 20µs
Repetitive T=400µs	δ Z_{th}	0.450 0.900	0.425 0.850	0.375 0.800	0.050 0.130
Single Shot T=∞	δ Z_{th}	0.000 0.130	0.000 0.125	0.000 0.120	0.000 0.040

Table 1a. Composite pulse parameters for time t_x

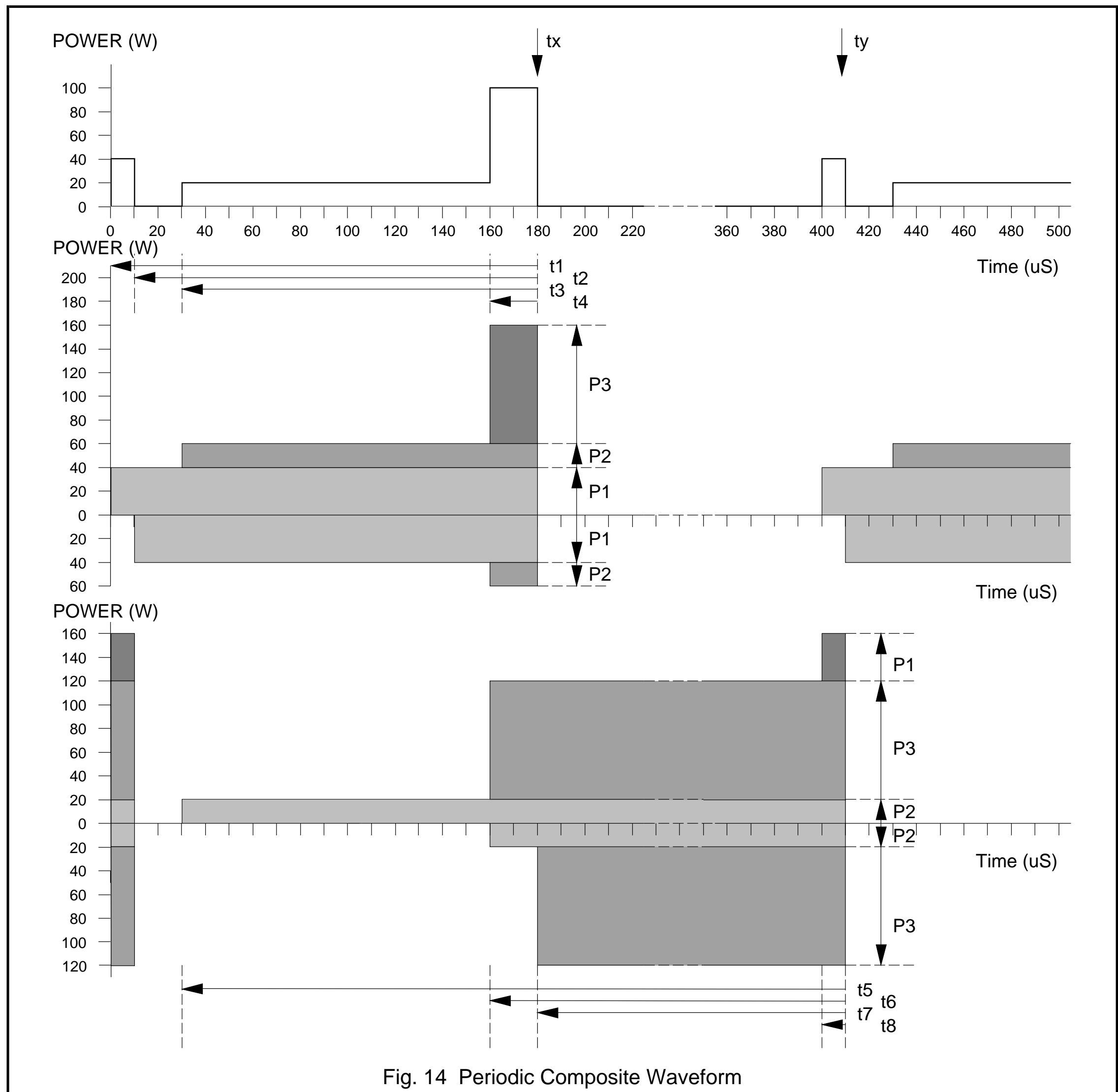

Fig. 14 Periodic Composite Waveform

Substituting these values into equation 15 for $T_{j\text{-}mb@x}$ gives

Repetitive:

$$\Delta T_{j-mb@x} = 40\times 0.9 + 20\times 0.85$$
$$+ 100\times 0.13 - 40\times 0.85$$
$$- 20\times 0.13$$
$$= 29.4°C$$

$$T_j = T_{mb} + \Delta T_{j-mb} = 75 + 29.4 = 104.4°C$$

Single Shot:

$$\Delta T_{j-mb@x} = 40\times 0.13 + 20\times 0.125$$
$$+ 100\times 0.04 - 40\times 0.125$$
$$- 20\times 0.04$$
$$= 5.9°C$$

$$T_j = T_{mb} + \Delta T_{j-mb} = 75 + 5.9 = 80.9°C$$

Hence the peak values of T_j are 104.4˚C for the repetitive case, and 80.9˚C for the single shot case.

Calculation for time t_y

$$\Delta T_{j-mb@y} = P_2.Z_{thj-mb(t5)} + P_3.Z_{thj-mb(t6)}$$
$$+ P_1.Z_{thj-mb(t8)} - P_2.Z_{thj-mb(t6)}$$
$$- P_3.Z_{thj-mb(t7)} \qquad 16$$

where $Z_{thj-mb(t)}$ is the transient thermal impedance for a pulse time t.

		t5 380µs	t6 250µs	t7 230µs	t8 10µs
Repetitive T=400µs	δ Z_{th}	0.950 1.950	0.625 1.300	0.575 1.250	0.025 0.080
Single Shot T=∞	δ Z_{th}	0.000 0.200	0.000 0.160	0.000 0.150	0.000 0.030

Table 1b. Composite pulse parameters for time t_y

Substituting these values into equation 16 for $T_{j-mb@y}$ gives

Repetitive:
$$\Delta T_{j-mb@y} = 20 \times 1.95 + 100 \times 1.3$$
$$+ 40 \times 0.08 - 20 \times 1.3$$
$$- 100 \times 1.25$$
$$= 21.2°C$$
$$T_j = T_{mb} + \Delta T_{j-mb} = 75 + 21.2 = 96.2°C$$

Single Shot:
$$\Delta T_{j-mb@y} = 20 \times 0.2 + 100 \times 0.16$$
$$+ 40 \times 0.03 - 20 \times 0.16$$
$$- 100 \times 0.15$$
$$= 3°C$$
$$T_j = T_{mb} + \Delta T_{j-mb} = 75 + 3 = 78°C$$

Hence the peak values of T_j are 96.2˚C for the repetitive case, and 78˚C for the single shot case.

The average power dissipation and the average junction temperature can be calculated as follows:

$$P_{av} = \frac{25 \times 10 + 5 \times 130 + 20 \times 100}{400}$$
$$= 7.25W$$
$$\Delta T_{j-mb(av)} = P_{av} \times Z_{thj-mb(\delta=1)} = 7.25 \times 2 = 14.5°C$$
$$T_{j(av)} = T_{mb} + \Delta T_{j-mb(av)} = 75 + 14.5 = 89.5°C$$

Clearly, the junction temperature at time t_x should be higher than that at time t_y, and this is proven in the above calculations.

Burst pulses

Power devices are frequently subjected to a burst of pulses. This type of signal can be treated as a composite waveform and as in the previous example simulated by superimposing several rectangular pulses which have a common period, but both positive and negative amplitudes, in addition to suitable values of t_p and δ.

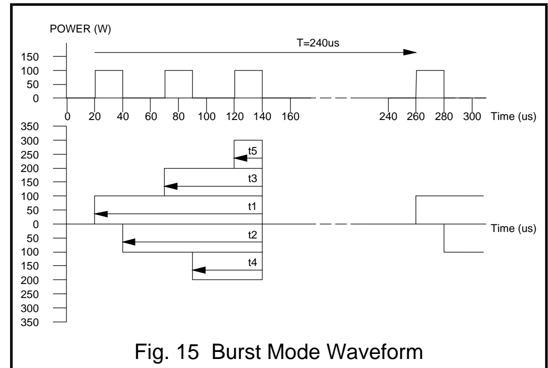

Fig. 15 Burst Mode Waveform

Consider the waveform shown in Fig. 15. The period is 240µs, and the burst consists of three rectangular pulses of 100W power and 20µs duration, separated by 30µs. The peak junction temperature will occur at the end of each burst at time t = t_x = 140µs. To be able to add the various effects of the pulses at this time, all the pulses, both positive and negative, must end at time t_x. Positive pulses increase the junction temperature, while negative pulses decrease it.

$$\Delta T_{j-mb@x} = P.Z_{thj-mb(t1)} + P.Z_{thj-mb(t3)}$$
$$+ P.Z_{thj-mb(t5)} - P.Z_{thj-mb(t2)}$$
$$- P.Z_{thj-mb(t4)} \qquad 17$$

where $Z_{thj-mb(t)}$ is the transient thermal impedance for a pulse time t.

The Z_{th} values are taken from Fig. 9. For each term in the equation, the equivalent duty cycle must be worked out. These values can then be used in conjunction with Fig. 9 to find a value for Z_{th}. Table 2 gives the values calculated for this example.

		t1 120µs	t2 100µs	t3 70µs	t4 50µs	t5 20µs
Repetitive T=240µs	δ Z_{th}	0.500 1.100	0.420 0.800	0.290 0.600	0.210 0.430	0.083 0.210
Single Shot T=∞	δ Z_{th}	0.000 0.100	0.000 0.090	0.000 0.075	0.000 0.060	0.000 0.040

Table 2. Burst Mode pulse parameters

Substituting these values into equation 17 gives

Repetitive:
$$\Delta T_{j-mb@x} = 100\times1.10 + 100\times0.60 + 100\times0.21 - 100\times0.80 - 100\times0.43 = 68°C$$

$$T_j = 75 + 68 = 143°C$$

Single Shot:
$$\Delta T_{j-mb@x} = 100\times0.10 + 100\times0.075 + 100\times0.04 - 100\times0.09 - 100\times0.06 = 6.5°C$$

$$T_j = 75 + 6.5 = 81.5°C$$

Hence the peak value of T_j is 143˚C for the repetitive case and 81.5˚C for the single shot case. To calculate the average junction temperature $T_{j(av)}$:

$$P_{av} = \frac{3\times100\times20}{240} = 25W$$

$$\Delta T_{j-mb(av)} = P_{av}\times Z_{thj-mb(\delta=1)} = 25\times2 = 50°C$$

$$T_{j(av)} = 75 + 50 = 125°C$$

The above example for the repetitive waveform highlights a case where the average junction temperature (125˚C) is well within limits but the composite pulse calculation shows the peak junction temperature to be significantly higher. For reasons of improved long term reliability it is usual to operate devices with a peak junction temperature below 125˚C.

Non-rectangular pulses

So far, the worked examples have only covered rectangular waveforms. However, triangular, trapeziodal and sinusoidal waveforms are also common. In order to apply the above thermal calculations to non rectangular waveforms, the waveform is approximated by a series of rectangles. Each rectangle represents part of the waveform. The equivalent rectangle must be equal in area to the section of the waveform it represents (ie the same energy) and also be of the same peak power. With reference to Fig. 16, a triangular waveform has been approximated to one rectangle in the first example, and two rectangles in the second. Obviously, increasing the number of sections the waveform is split into will improve the accuracy of the thermal calculations.

In the first example, there is only one rectanglular pulse , of duration 50µs, dissipating 50W. So again using equation 14 and a rearrangement of equation 7:

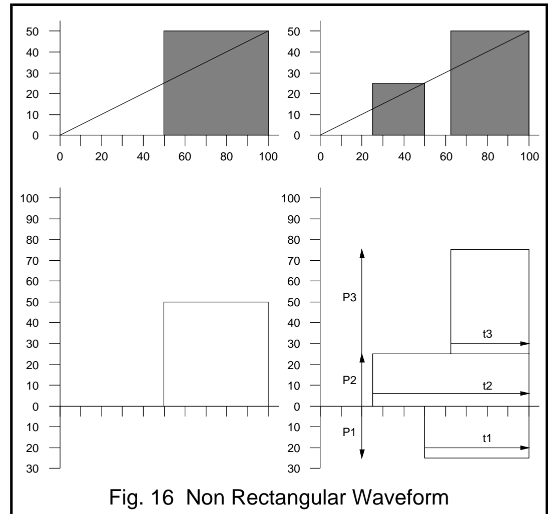

Fig. 16 Non Rectangular Waveform

$$\Delta T_{j-mb} = P_{tot\,M}\times Z_{thj-mb}$$

Single Shot
$$\Delta T_{j-mb} = 50\times0.065 = 3.25°C$$
$$T_{jpeak} = 75 + 3.25 = 78.5°C$$

10% Duty cycle
$$\Delta T_{j-mb} = 50\times0.230 = 11.5°C$$
$$T_{jpeak} = 75 + 11.5 = 86.5°C$$

50% Duty cycle
$$\Delta T_{j-mb} = 50\times1.000 = 50°C$$
$$T_{jpeak} = 75 + 50 = 125°C$$

When the waveform is split into two rectangular pulses:

$$\Delta T_{j-mb} = P_3.Z_{thj-mb(t3)} + P_1.Z_{thj-mb(t1)} - P_2.Z_{thj-mb(t2)} \quad 18$$

For this example P_1 = 25W, P_2 = 25W, P_3 = 50W. Table 3 below shows the rest of the parameters:

		t1 75µs	t2 50µs	t3 37.5µs
Single Shot T=∞	D Z_{th}	0.000 0.085	0.000 0.065	0.000 0.055
10% Duty Cycle T=1000µs	D Z_{th}	0.075 0.210	0.050 0.140	0.037 0.120
50% Duty Cycle T=200µs	D Z_{th}	0.375 0.700	0.250 0.500	0.188 0.420

Table 3. Non Rectangular Pulse Calculations

Sustituting these values into equation 18 gives:

Single shot $\Delta T_{j-mb} = 50 \times 0.055 + 25 \times 0.085 - 25 \times 0.065$

$= 3.25°C$

$T_{jpeak} = 75 + 3.25 = 78.5°C$

10% Duty cycle $\Delta T_{j-mb} = 50 \times 0.12 + 25 \times 0.21 - 25 \times 0.14$

$= 7.75°C$

$T_{jpeak} = 75 + 7.75 = 82.5°C$

50% Duty cycle $\Delta T_{j-mb} = 50 \times 0.42 + 25 \times 0.7 - 25 \times 0.5$

$= 26°C$

$T_{jpeak} = 75 + 26 = 101°C$

To calculate the average junction temperature:

10% Duty Cycle $P_{av} = \frac{50 \times 50}{1000}$

$= 2.5W$

$\Delta T_{j-mb(av)} = P_{av} \times Z_{thj-mb(\delta=1)} = 2.5 \times 2 = 5°C$

$T_{j(av)} = 75 + 5 = 80°C$

50% Duty Cycle $P_{av} = \frac{50 \times 50}{200}$

$= 12.5W$

$\Delta T_{j-mb(av)} = P_{av} \times Z_{thj-mb(\delta=1)} = 12.5 \times 2 = 25°C$

$T_{j(av)} = 75 + 25 = 100°C$

Conclusion

A method has been presented to allow the calculation of average and peak junction temperatures for a variety of pulse types. Several worked examples have shown calculations for various common waveforms. The method for non rectangular pulses can be applied to any wave shape, allowing temperature calculations for waveforms such as exponential and sinusoidal power pulses. For pulses such as these, care must be taken to ensure that the calculation gives the peak junction temperature, as it may not occur at the end of the pulse. In this instance several calculations must be performed with different endpoints to find the maximum junction temperature.

7.1.2 Heat Dissipation

All semiconductor failure mechanisms are temperature dependent and so the lower the junction temperature, the higher the reliability of the circuit. Thus our data specifies a maximum junction temperature which should not be exceeded under the worst probable conditions. However, derating the operating temperature from T_{jmax} is always desirable to improve the reliability still further. The junction temperature depends on both the power dissipated in the device and the thermal resistances (or impedances) associated with the device. Thus careful consideration of these thermal resistances (or impedances) allows the user to calculate the maximum power dissipation that will keep the junction temperature below a chosen value.

The formulae and diagrams given in this section can only be considered as a guide for determining the nature of a heatsink. This is because the thermal resistance of a heatsink depends on numerous parameters which cannot be predetermined. They include the position of the transistor on the heatsink, the extent to which air can flow unhindered, the ratio of the lengths of the sides of the heatsink, the screening effect of nearby components, and heating from these components. It is always advisable to check important temperatures in the finished equipment under the worst probable operating conditions. The more complex the heat dissipation conditions, the more important it becomes to carry out such checks.

Heat flow path

The heat generated in a semiconductor chip flows by various paths to the surroundings. Small signal devices do not usually require heatsinking; the heat flows from the junction to the mounting base which is in close contact with the case. Heat is then lost by the case to the surroundings by convection and radiation (Fig. 1a). Power transistors, however, are usually mounted on heatsinks because of the higher power dissipation they experience. Heat flows from the transistor case to the heatsink by way of contact pressure, and the heatsink loses heat to the surroundings by convection and radiation, or by conduction to cooling water (Fig. 1b). Generally air cooling is used so that the ambient referred to in Fig.1 is usually the surrounding air. Note that if this is the air inside an equipment case, the additional thermal resistance between the inside and outside of the equipment case should be taken into account.

Contact thermal resistance $R_{th\,mb-h}$

The thermal resistance between the transistor mounting base and the heatsink depends on the quality and size of the contact areas, the type of any intermediate plates used, and the contact pressure. Care should be taken when drilling holes in heatsinks to avoid burring and distorting the metal, and both mating surfaces should be clean. Paint finishes of normal thickness, up to 50 um (as a protection against electrolytic voltage corrosion), barely affect the thermal resistance. Transistor case and heatsink surfaces can never be perfectly flat, and so contact will take place on several points only, with a small air-gap over the rest of the area. The use of a soft substance to fill this gap lowers the contact thermal resistance. Normally, the gap is filled with a heatsinking compound which remains fairly viscous at normal transistor operating temperatures and has a high thermal conductivity. The use of such a compound also prevents moisture from penetrating between the contact surfaces. Proprietary heatsinking compounds are available which consist of a silicone grease loaded with some electrically insulating good thermally conducting powder such as alumina. The contact thermal resistance $R_{th\,mb-h}$ is usually small with respect to ($R_{th\,j-mb}$ + $R_{th\,h-amb}$) when cooling is by natural convection. However, the heatsink thermal resistance $R_{th\,h-amb}$ can be very small when either forced ventilation or water cooling are used, and thus a close thermal contact between the transistor case and heatsink becomes particularly important.

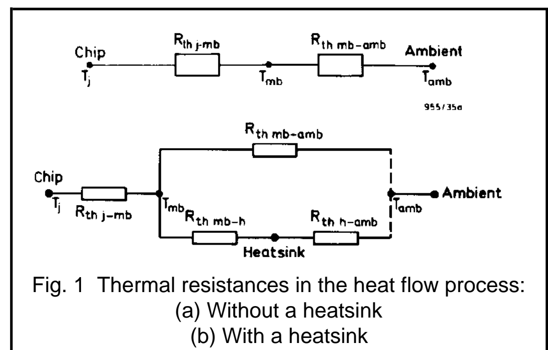

Fig. 1 Thermal resistances in the heat flow process:
(a) Without a heatsink
(b) With a heatsink

Thermal resistance calculations

Fig. 1a shows that, when a heatsink is not used, the total thermal resistance between junction and ambient is given by:

$$R_{thj-amb} = R_{thj-mb} + R_{thmb-amb} \qquad 1$$

However, power transistors are generally mounted on a heatsink since $R_{th\,j-amb}$ is not usually small enough to maintain temperatures within the chip below desired levels.

Fig. 1b shows that, when a heatsink is used, the total thermal resistance is given by:

$$R_{thj-amb} = R_{thj-mb} + R_{thmb-h} + R_{thh-amb} \qquad 2$$

Note that the direct heat loss from the transistor case to the surroundings through $R_{th\ mb\text{-}amb}$ is negligibly small.

The first stage in determining the size and nature of the required heatsink is to calculate the maximum heatsink thermal resistance $R_{th\ h\text{-}amb}$ that will maintain the junction temperature below the desired value

Continuous operation

Under dc conditions, the maximum heatsink thermal resistance can be calculated directly from the maximum desired junction temperature.

$$R_{thj-amb} = \frac{T_j - T_{amb}}{P_{tot(av)}} \qquad 3$$

and

$$R_{thj-mb} = \frac{T_j - T_{mb}}{P_{tot(av)}} \qquad 4$$

Combining equations 2 and 3 gives:

$$R_{thh-amb} = \frac{T_j - T_{amb}}{P_{tot(av)}} - R_{thj-mb} - R_{thmb-h} \qquad 5$$

and substituting Eq 4 into Eq 5 gives:

$$R_{thh-amb} = \frac{T_{mb} - T_{amb}}{P_{tot(av)}} - R_{thmb-h} \qquad 6$$

The values of $R_{th\ j\text{-}mb}$ and $R_{th\ mb\text{-}h}$ are given in the published data. Thus, either Eq. 5 or Eq.6 can be used to find the maximum heatsink thermal resistance.

Intermittent operation

The thermal equivalent circuits of Fig. 1 are inappropriate for intermittent operation, and the thermal impedance $Z_{th\ j\text{-}mb}$ should be considered.

$$P_{totM} = \frac{T_j - T_{mb}}{Z_{thj-mb}}$$

thus:

$$T_{mb} = T_j - P_{totM}.Z_{thj-mb} \qquad 7$$

The mounting-base temperature has always been assumed to remain constant under intermittent operation. This assumption is known to be valid in practice provided that the pulse time is less than about one second. The mounting-base temperature does not change significantly under these conditions as indicated in Fig. 2. This is because heatsinks have a high thermal capacity and thus a high thermal time-constant.

Thus Eq.6 is valid for intermittent operation, provided that the pulse time is less than one second. The value of Tmb can be calculated from Eq. 7, and the heatsink thermal resistance can be obtained from Eq.6.

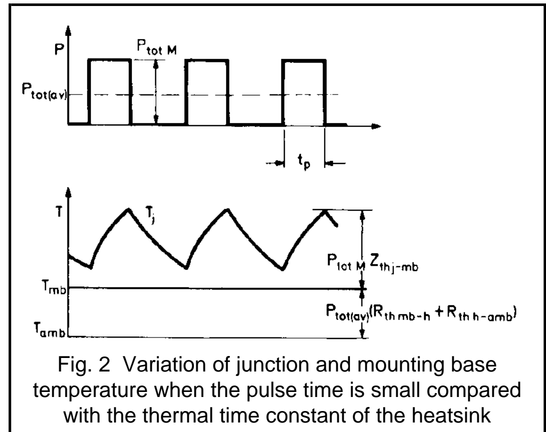

Fig. 2 Variation of junction and mounting base temperature when the pulse time is small compared with the thermal time constant of the heatsink

The thermal time constant of a transistor is defined as that time at which the junction temperature has reached 70% of its final value after being subjected to a constant power dissipation at a constant mounting base temperature.

Now, if the pulse duration tp exceeds one second, the transistor is temporarily in thermal equilibrium since such a pulse duration is significantly greater than the thermal time-constant of most transistors. Consequently, for pulse times of more than one second, the temperature difference T_j - T_{mb} reaches a stationary final value (Fig. 3) and Eq.7 should be replaced by:

$$T_{mb} = T_j - P_{totM}.R_{thj-mb} \qquad 8$$

In addition, it is no longer valid to assume that the mounting base temperature is constant since the pulse time is also no longer small with respect to the thermal time constant of the heatsink.

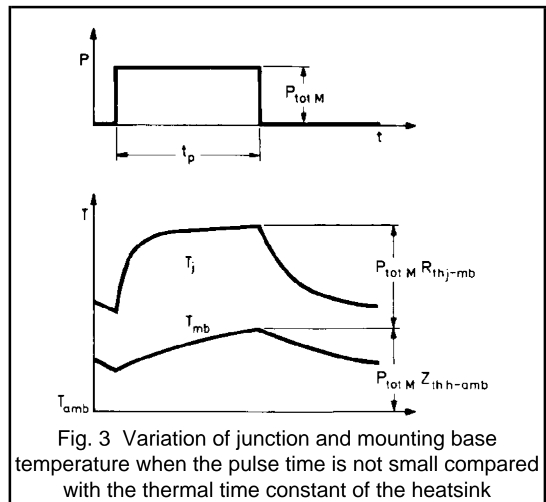

Fig. 3 Variation of junction and mounting base temperature when the pulse time is not small compared with the thermal time constant of the heatsink

Smaller heatsinks for intermittent operation

In many instances, the thermal capacity of a heatsink can be utilised to design a smaller heatsink for intermittent operation than would be necessary for the same level of continuous power dissipation. The average power dissipation in Eq. 6 is replaced by the peak power dissipation to obtain the value of the thermal impedance between the heatsink and the surroundings

$$Z_{thh-amb} = \frac{T_{mb} - T_{amb}}{P_{totM}} - R_{thmb-h} \qquad 9$$

The value of $Z_{th\ h\text{-}amb}$ will be less than the comparable thermal resistance and thus a smaller heatsink can be designed than that obtained using the too large value calculated from Eq.6.

Heatsinks

Three varieties of heatsink are in common use: flat plates (including chassis), diecast finned heatsinks, and extruded finned heatsinks. The material normally used for heatsink construction is aluminium although copper may be used with advantage for flat-sheet heatsinks. Small finned clips are sometimes used to improve the dissipation of low-power transistors.

Heatsink finish

Heatsink thermal resistance is a function of surface finish. A painted surface will have a greater emissivity than a bright unpainted one. The effect is most marked with flat plate heatsinks, where about one third of the heat is dissipated by radiation. The colour of the paint used is relatively unimportant, and the thermal resistance of a flat plate heatsink painted gloss white will be only about 3% higher than that of the same heatsink painted matt black. With finned heatsinks, painting is less effective since heat radiated from most fins will fall on adjacent fins but it is still worthwhile. Both anodising and etching will decrease the thermal resistivity. Metallic type paints, such as aluminium paint, have the lowest emissivities, although they are approximately ten times better than a bright aluminium metal finish.

Flat-plate heatsinks

The simplest type of heatsink is a flat metal plate to which the transistor is attached. Such heatsinks are used both in the form of separate plates and as the equipment chassis itself. The thermal resistance obtained depends on the thickness, area and orientation of the plate, as well as on the finish and power dissipated. A plate mounted horizontally will have about twice the thermal resistance of a vertically mounted plate. This is particularly important where the equipment chassis itself is used as the heatsink.

In Fig. 4, the thermal resistance of a blackened heatsink is plotted against surface area (one side) with power dissipation as a parameter. The graph is accurate to within 25% for nearly square plates, where the ratio of the lengths of the sides is less than 1.25:1.

Finned heatsinks

Finned heatsinks may be made by stacking flat plates, although it is usually more economical to use ready made diecast or extruded heatsinks. Since most commercially available finned heatsinks are of reasonably optimum design, it is possible to compare them on the basis of the overall volume which they occupy. This comparison is made in Fig. 5 for heatsinks with their fins mounted vertically; again, the graph is accurate to 25%.

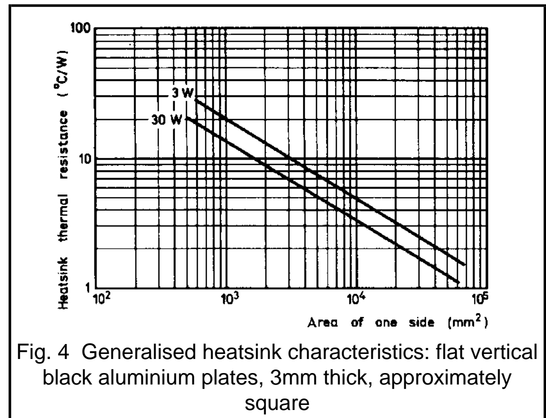

Fig. 4 Generalised heatsink characteristics: flat vertical black aluminium plates, 3mm thick, approximately square

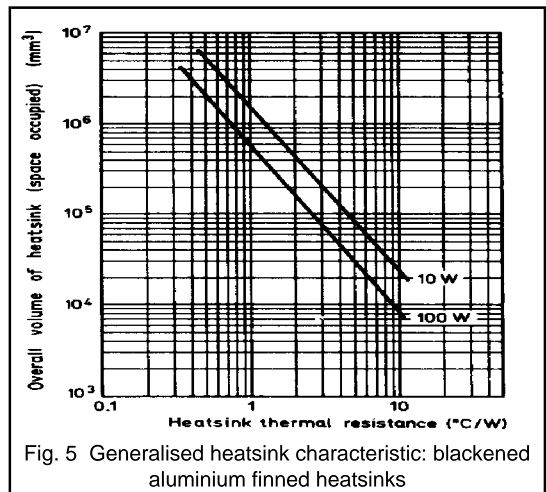

Fig. 5 Generalised heatsink characteristic: blackened aluminium finned heatsinks

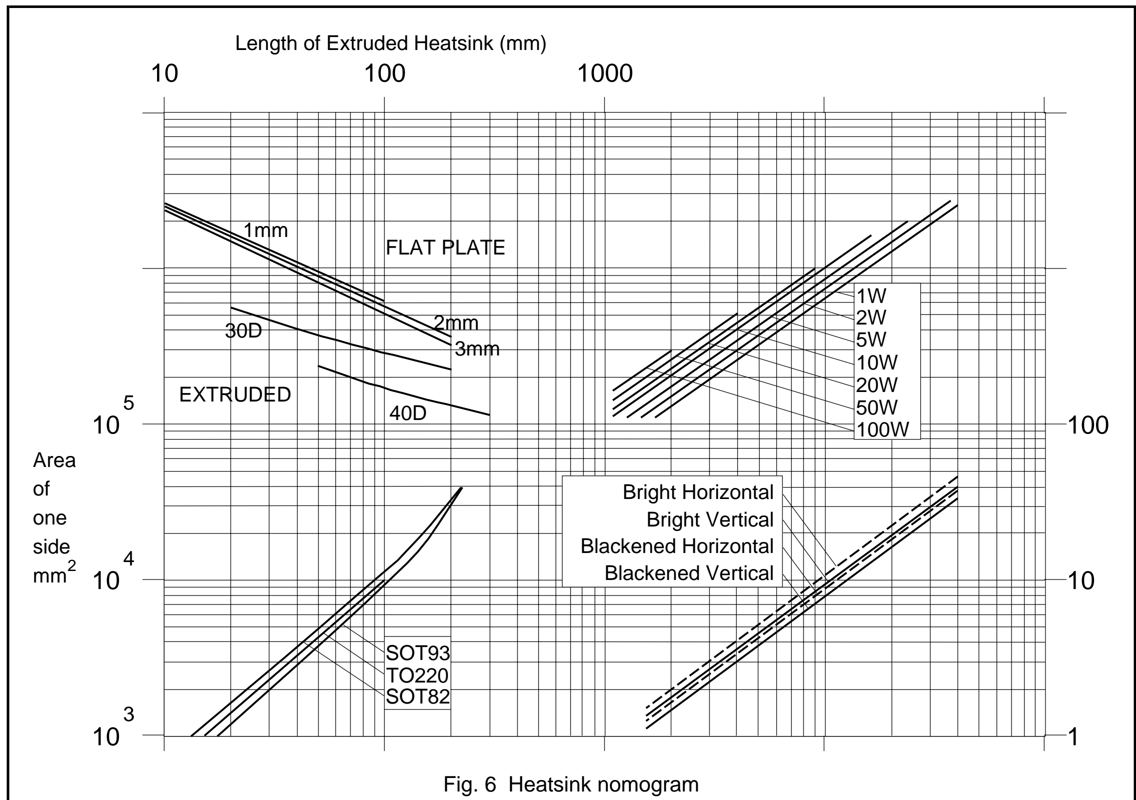

Fig. 6 Heatsink nomogram

Heatsink dimensions

The maximum thermal resistance through which sufficient power can be dissipated without damaging the transistor can be calculated as discussed previously. This section explains how to arrive at a type and size of heatsink that gives a sufficiently low thermal resistance.

Natural air cooling

The required size of aluminium heatsinks - whether flat or extruded (finned) can be derived from the nomogram in Fig. 6. Like all heatsink diagrams, the nomogram does not give exact values for $R_{th\ h\text{-}amb}$ as a function of the dimensions since the practical conditions always deviate to some extent from those under which the nomogram was drawn up. The actual values for the heatsink thermal resistance may differ by up to 10% from the nomogram values. Consequently, it is advisable to take temperature measurements in the finished equipment, particularly where the thermal conditions are critical.

The conditions to which the nomogram applies are as follows:

- natural air cooling (unimpeded natural convection with no build up of heat);
- ambient temperature about 25˚C, measured about 50mm below the lower edge of the heatsink (see Fig. 7);
- atmospheric pressure about 10 N/m^2;
- single mounting (that is, not affected by nearby heatsinks);
- distance between the bottom of the heatsink and the base of a draught-free space about 100mm (see Fig. 7);
- transistor mounted roughly in the centre of the heatsink (this is not so important for finned heatsinks because of the good thermal conduction).

The appropriately-sized heatsink is found as follows.

1. Enter the nomogram from the right hand side of section 1 at the appropriate $R_{th\ h\text{-}amb}$ value (see Fig. 8). Move horizontally to the left, until the appropriate curve for orientation and surface finish is reached.
2. Move vertically upwards to intersect the appropriate power dissipation curve in section 2.

3. Move horizontally to the left into section 3 for the desired thickness of a flat-plate heatsink, or the type of extrusion.
4. If an extruded heatsink is required, move vertically upwards to obtain its length (Figs. 9a and 9b give the outlines of the extrusions).
5. If a flat-plate heatsink is to be used, move vertically downwards to intersect the appropriate curve for envelope type in section 4.
6. Move horizontally to the left to obtain heatsink area.
7. The heatsink dimensions should not exceed the ratio of 1.25:1.

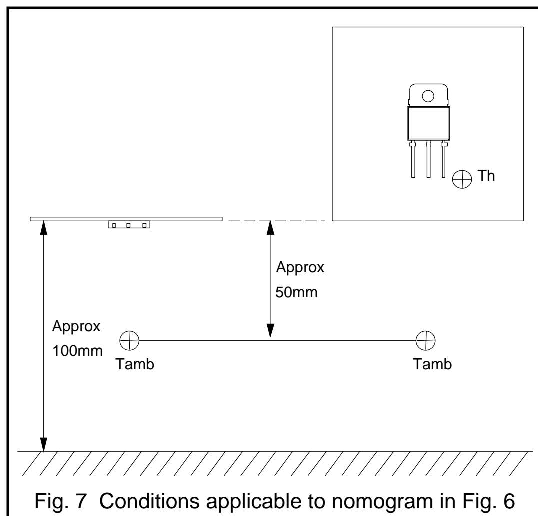

Fig. 7 Conditions applicable to nomogram in Fig. 6

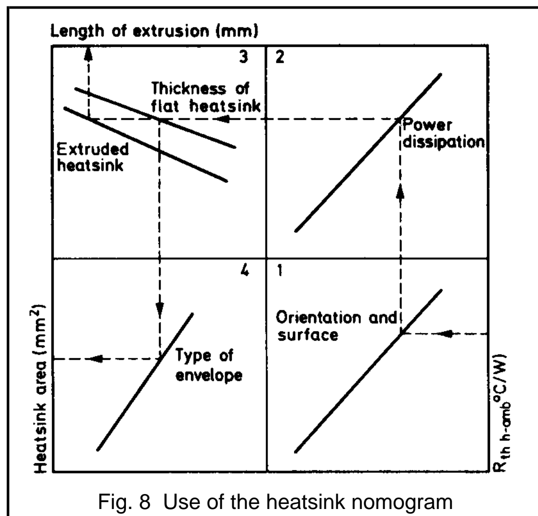

Fig. 8 Use of the heatsink nomogram

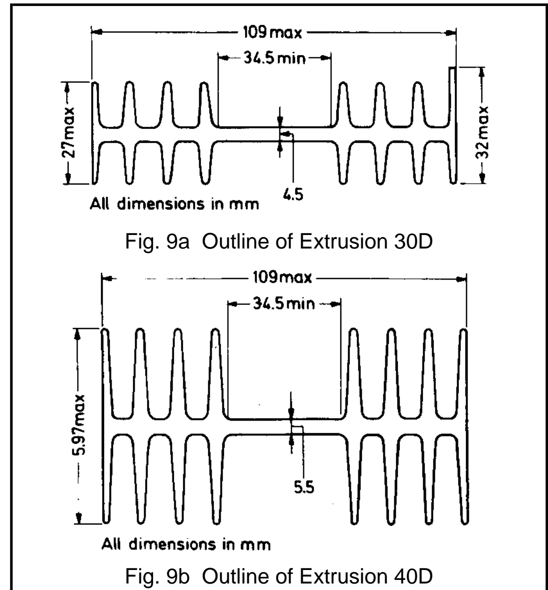

Fig. 9a Outline of Extrusion 30D

Fig. 9b Outline of Extrusion 40D

The curves in section 2 take account of the non linear nature of the relationship between the temperature drop across the heatsink and the power dissipation loss. Thus, at a constant value of the heatsink thermal resistance, the greater the power dissipation, the smaller is the required size of heatsink. This is illustrated by the following example.

Example

An extruded heatsink mounted vertically and with a painted surface is required to have a maximum thermal resistance of $R_{th\ h\text{-}amb}$ = 2.6 ˚C/W at the following powers:

$$(a)P_{tot(av)} = 5W \quad (b)P_{tot(av)} = 50W$$

Enter the nomogram at the appropriate value of the thermal resistance in section 1, and via either the 50W or 5W line in section 2, the appropriate lengths of the extruded heatsink 30D are found to be:

(a) length = 110mm and (b) length = 44mm.

Case (b) requires a shorter length since the temperature difference is ten times greater than in case (a).

As the ambient temperature increases beyond 25˚C, so does the temperature of the heatsink and thus the thermal resistance (at constant power) decreases owing to the increasing role of radiation in the heat removal process. Consequently, a heatsink with dimensions derived from Fig. 6 at T_{amb} > 25˚C will be more than adequate. If the maximum ambient temperature is less than 25˚C, then the thermal resistance will increase slightly. However, any

increase will lie within the limits of accuracy of the nomogram and within the limits set by other uncertainties associated with heatsink calculations.

For heatsinks with relatively small areas, a considerable part of the heat is dissipated from the transistor case. This is why the curves in section 4 tend to flatten out with decreasing heatsink area. The area of extruded heatsinks is always large with respect to the surface of the transistor case, even when the length is small.

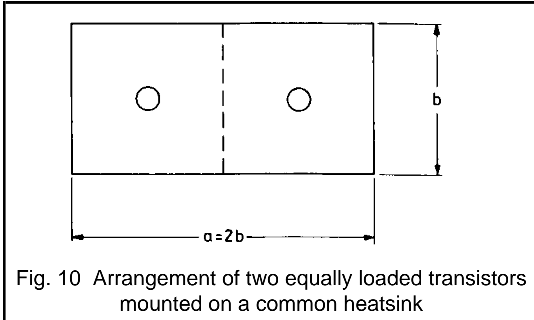

Fig. 10 Arrangement of two equally loaded transistors mounted on a common heatsink

If several transistors are mounted on a common heatsink, each transistor should be associated with a particular section of the heatsink (either an area or length according to type) whose maximum thermal resistance is calculated from equations 5 or 6; that is, without taking the heat produced by nearby transistors into account. From the sum of these areas or lengths, the size of the common heatsink can then be obtained. If a flat heatsink is used, the transistors are best arranged as shown in Fig. 10. The maximum mounting base temperatures of transistors in such a grouping should always be checked once the equipment has been constructed.

Forced air cooling

If the thermal resistance needs to be much less than 1˚C/W, or the heatsink not too large, forced air cooling by means of fans can be provided. Apart from the size of the heatsink, the thermal resistance now only depends on the speed of the cooling air. Provided that the cooling air flows parallel to the fins and with sufficient speed (>0.5m/s), the thermal resistance hardly depends on the power dissipation and the orientation of the heatsink. Note that turbulence in the air current can result in practical values deviating from theoretical values.

Fig. 11 shows the form in which the thermal resistances for forced air cooling are given in the case of extruded heatsinks. It also shows the reduction in thermal resistance or length of heatsink which may be obtained with forced air cooling.

The effect of forced air cooling in the case of flat heatsinks is seen from Fig. 12. Here, too, the dissipated power and the orientation of the heatsink have only a slight effect on the thermal resistance, provided that the air flow is sufficiently fast.

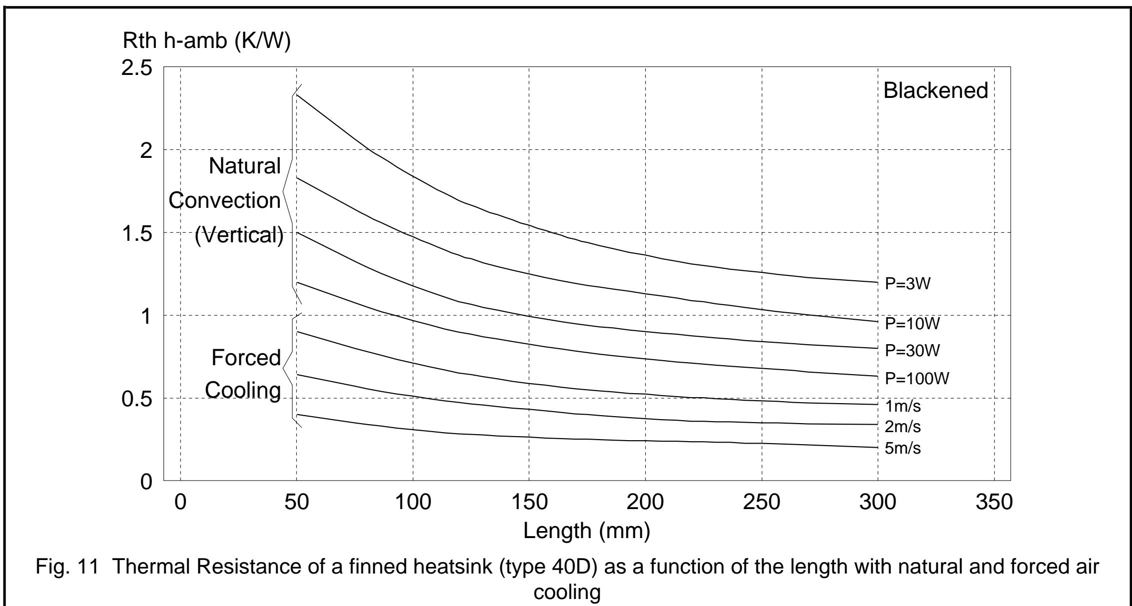

Fig. 11 Thermal Resistance of a finned heatsink (type 40D) as a function of the length with natural and forced air cooling

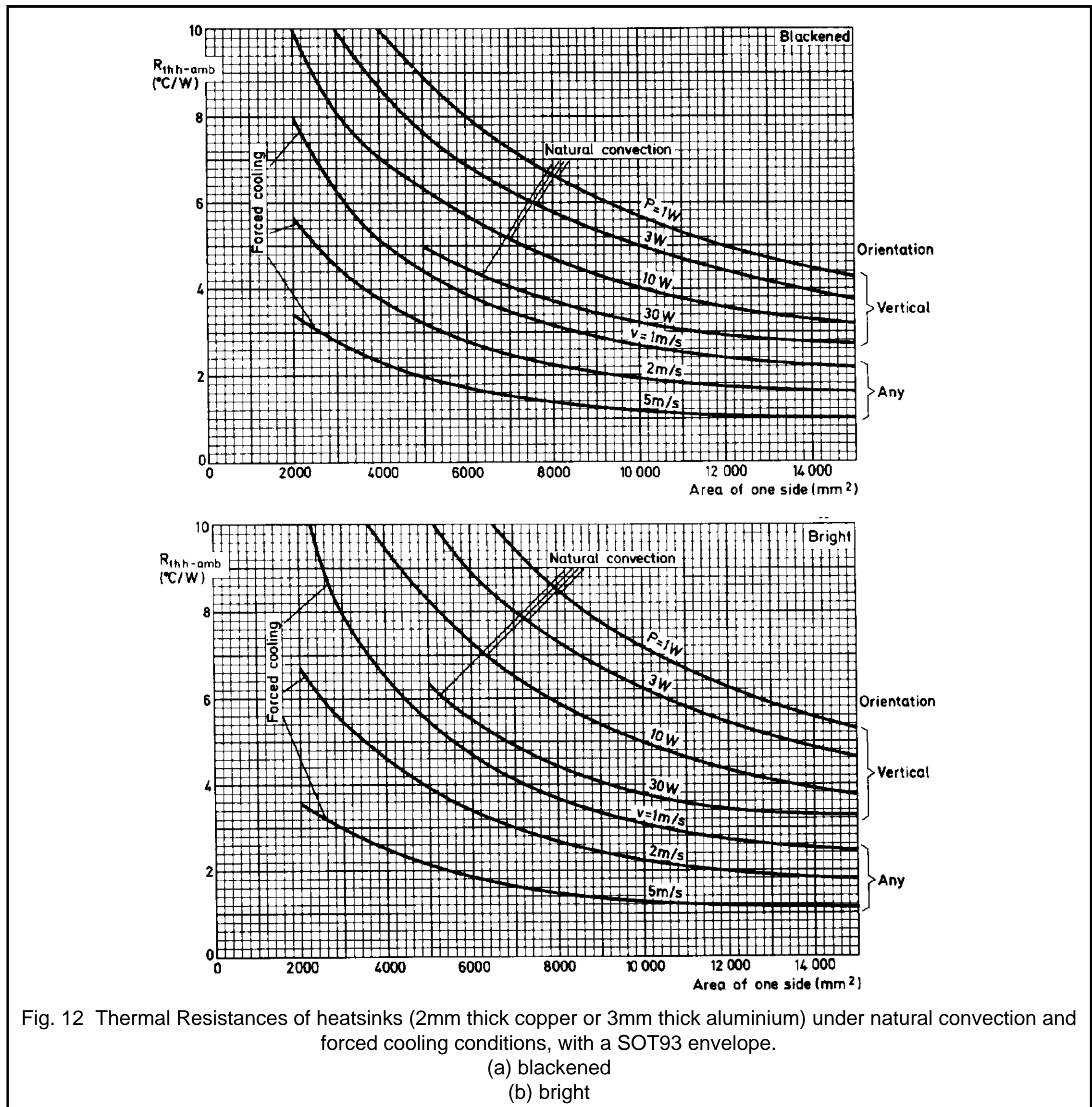

Fig. 12 Thermal Resistances of heatsinks (2mm thick copper or 3mm thick aluminium) under natural convection and forced cooling conditions, with a SOT93 envelope.
(a) blackened
(b) bright

Summary

The majority of power transistors require heatsinking, and once the maximum thermal resistance that will maintain the device’s junction temperature below its rating has been calculated, a heatsink of appropriate type and size can be chosen. The practical conditions under which a transistor will be operated are likely to differ from the theoretical considerations used to determine the required heatsink, and thus temperatures should always be checked in the finished equipment. Finally, some applications require a small heatsink, or one with a very low thermal resistance, in which case forced air cooling by means of fans should be provided.

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Preface

This book was prepared by the Power Semiconductor Applications Laboratory of the Philips Semiconductors product division, Hazel Grove. The book is intended as a guide to using power semiconductors both efficiently and reliably in power conversion applications. It is made up of eight main chapters each of which contains a number of application notes aimed at making it easier to select and use power semiconductors.

CHAPTER 1 forms an introduction to power semiconductors concentrating particularly on the two major power transistor technologies, Power MOSFETs and High Voltage Bipolar Transistors.

CHAPTER 2 is devoted to Switched Mode Power Supplies. It begins with a basic description of the most commonly used topologies and discusses the major issues surrounding the use of power semiconductors including rectifiers. Specific design examples are given as well as a look at designing the magnetic components. The end of this chapter describes resonant power supply technology.

CHAPTER 3 describes motion control in terms of ac, dc and stepper motor operation and control. This chapter looks only at transistor controls, phase control using thyristors and triacs is discussed separately in chapter 6.

CHAPTER 4 looks at television and monitor applications. A description of the operation of horizontal deflection circuits is given followed by transistor selection guides for both deflection and power supply applications. Deflection and power supply circuit examples are also given based on circuits designed by the Product Concept and Application Laboratories (Eindhoven).

CHAPTER 5 concentrates on automotive electronics looking in detail at the requirements for the electronic switches taking into consideration the harsh environment in which they must operate.

CHAPTER 6 reviews thyristor and triac applications from the basics of device technology and operation to the simple design rules which should be followed to achieve maximum reliability. Specific examples are given in this chapter for a number of the common applications.

CHAPTER 7 looks at the thermal considerations for power semiconductors in terms of power dissipation and junction temperature limits. Part of this chapter is devoted to worked examples showing how junction temperatures can be calculated to ensure the limits are not exceeded. Heatsink requirements and designs are also discussed in the second half of this chapter.

CHAPTER 8 is an introduction to the use of high voltage bipolar transistors in electronic lighting ballasts. Many of the possible topologies are described.

Table of Contents

CHAPTER 1 Introduction to Power Semiconductors 1

General 3

1.1.1 An Introduction To Power Devices 5

Power MOSFET 17

1.2.1 PowerMOS Introduction 19
1.2.2 Understanding Power MOSFET Switching Behaviour 29
1.2.3 Power MOSFET Drive Circuits 39
1.2.4 Parallel Operation of Power MOSFETs 49
1.2.5 Series Operation of Power MOSFETs 53
1.2.6 Logic Level FETS 57
1.2.7 Avalanche Ruggedness 61
1.2.8 Electrostatic Discharge (ESD) Considerations 67
1.2.9 Understanding the Data Sheet: PowerMOS 69

High Voltage Bipolar Transistor 77

1.3.1 Introduction To High Voltage Bipolar Transistors 79
1.3.2 Effects of Base Drive on Switching Times 83
1.3.3 Using High Voltage Bipolar Transistors 91
1.3.4 Understanding The Data Sheet: High Voltage Transistors 97

CHAPTER 2 Switched Mode Power Supplies 103

Using Power Semiconductors in Switched Mode Topologies 105

2.1.1 An Introduction to Switched Mode Power Supply Topologies 107
2.1.2 The Power Supply Designer's Guide to High Voltage Transistors 129
2.1.3 Base Circuit Design for High Voltage Bipolar Transistors in Power Converters 141
2.1.4 Isolated Power Semiconductors for High Frequency Power Supply Applications 153

Output Rectification 159

2.2.1 Fast Recovery Epitaxial Diodes for use in High Frequency Rectification 161
2.2.2 Schottky Diodes from Philips Semiconductors 173
2.2.3 An Introduction to Synchronous Rectifier Circuits using PowerMOS Transistors 179

Design Examples 185

2.3.1 Mains Input 100 W Forward Converter SMPS: MOSFET and Bipolar Transistor Solutions featuring ETD Cores 187
2.3.2 Flexible, Low Cost, Self-Oscillating Power Supply using an ETD34 Two-Part Coil Former and 3C85 Ferrite 199

Magnetics Design 205

2.4.1 Improved Ferrite Materials and Core Outlines for High Frequency Power Supplies 207

Resonant Power Supplies 217

2.5.1. An Introduction To Resonant Power Supplies 219
2.5.2. Resonant Power Supply Converters - The Solution For Mains Pollution Problems 225

CHAPTER 3 Motor Control 241

AC Motor Control 243

3.1.1 Noiseless A.C. Motor Control: Introduction to a 20 kHz System 245
3.1.2 The Effect of a MOSFET's Peak to Average Current Rating on Invertor Efficiency 251
3.1.3 MOSFETs and FREDFETs for Motor Drive Equipment 253
3.1.4 A Designers Guide to PowerMOS Devices for Motor Control 259
3.1.5 A 300V, 40A High Frequency Inverter Pole Using Paralleled FREDFET Modules 273

DC Motor Control 283

3.2.1 Chopper circuits for DC motor control 285
3.2.2 A switched-mode controller for DC motors 293
3.2.3 Brushless DC Motor Systems 301

Stepper Motor Control 307

3.3.1 Stepper Motor Control 309

CHAPTER 4 Televisions and Monitors 317

Power Devices in TV & Monitor Applications (including selection guides) 319

4.1.1 An Introduction to Horizontal Deflection 321
4.1.2 The BU25XXA/D Range of Deflection Transistors 331

4.1.3 Philips HVT's for TV & Monitor Applications 339
4.1.4 TV and Monitor Damper Diodes 345

TV Deflection Circuit Examples 349

4.2.1 Application Information for the 16 kHz Black Line Picture Tubes 351
4.2.2 32 kHz / 100 Hz Deflection Circuits for the 66FS Black Line Picture Tube 361

SMPS Circuit Examples 377

4.3.1 A 70W Full Performance TV SMPS Using The TDA8380 379
4.3.2 A Synchronous 200W SMPS for 16 and 32 kHz TV 389

Monitor Deflection Circuit Example 397

4.4.1 A Versatile 30 - 64 kHz Autosync Monitor 399

CHAPTER 5 Automotive Power Electronics 421

Automotive Motor Control (including selection guides) 423

5.1.1 Automotive Motor Control With Philips MOSFETS 425

Automotive Lamp Control (including selection guides) 433

5.2.1 Automotive Lamp Control With Philips MOSFETS 435

The TOPFET 443

5.3.1 An Introduction to the 3 pin TOPFET 445
5.3.2 An Introduction to the 5 pin TOPFET 447
5.3.3 BUK101-50DL - a Microcontroller compatible TOPFET 449
5.3.4 Protection with 5 pin TOPFETs 451
5.3.5 Driving TOPFETs 453
5.3.6 High Side PWM Lamp Dimmer using TOPFET 455
5.3.7 Linear Control with TOPFET 457
5.3.8 PWM Control with TOPFET 459
5.3.9 Isolated Drive for TOPFET 461
5.3.10 3 pin and 5 pin TOPFET Leadforms 463
5.3.11 TOPFET Input Voltage 465
5.3.12 Negative Input and TOPFET 467
5.3.13 Switching Inductive Loads with TOPFET 469
5.3.14 Driving DC Motors with TOPFET 471
5.3.15 An Introduction to the High Side TOPFET 473
5.3.16 High Side Linear Drive with TOPFET 475

Automotive Ignition 477

5.4.1 An Introduction to Electronic Automotive Ignition 479
5.4.2 IGBTs for Automotive Ignition 481
5.4.3 Electronic Switches for Automotive Ignition 483

CHAPTER 6 Power Control with Thyristors and Triacs 485

Using Thyristors and Triacs 487

6.1.1 Introduction to Thyristors and Triacs 489
6.1.2 Using Thyristors and Triacs 497
6.1.3 The Peak Current Handling Capability of Thyristors 505
6.1.4 Understanding Thyristor and Triac Data 509

Thyristor and Triac Applications 521

6.2.1 Triac Control of DC Inductive Loads 523
6.2.2 Domestic Power Control with Triacs and Thyristors 527
6.2.3 Design of a Time Proportional Temperature Controller 537

Hi-Com Triacs 547

6.3.1 Understanding Hi-Com Triacs 549
6.3.2 Using Hi-Com Triacs 551

CHAPTER 7 Thermal Management 553

Thermal Considerations 555

7.1.1 Thermal Considerations for Power Semiconductors 557
7.1.2 Heat Dissipation 567

CHAPTER 8 Lighting 575

Fluorescent Lamp Control 577

8.1.1 Efficient Fluorescent Lighting using Electronic Ballasts 579
8.1.2 Electronic Ballasts - Philips Transistor Selection Guide 587
8.1.3 An Electronic Ballast - Base Drive Optimisation 589

Index

Airgap, transformer core, 111, 113
Anti saturation diode, 590
Asynchronous, 497
Automotive
  fans
    see motor control
  IGBT, 481, 483
  ignition, 479, 481, 483
  lamps, 435, 455
  motor control, 425, 457, 459, 471, 475
  resistive loads, 442
  reverse battery, 452, 473, 479
  screen heater, 442
  seat heater, 442
  solenoids, 469
  TOPFET, 473
Avalanche, 61
Avalanche breakdown
  thyristor, 490
Avalanche multiplication, 134

Baker clamp, 138, 187, 190
Ballast
  electronic, 580
  fluorescent lamp, 579
  switchstart, 579
Base drive, 136
  base inductor, 147
  base inductor, diode assisted, 148
  base resistor, 146
  drive transformer, 145
  drive transformer leakage inductance, 149
  electronic ballast, 589
  forward converter, 187
  power converters, 141
  speed-up capacitor, 143
Base inductor, 144, 147
Base inductor, diode assisted, 148
Boost converter, 109
  continuous mode, 109
  discontinuous mode, 109
  output ripple, 109
Bootstrap, 303
Breakback voltage
  diac, 492
Breakdown voltage, 70
Breakover current
  diac, 492
Breakover voltage
  diac, 492, 592
  thyristor, 490
Bridge circuits
  see Motor Control - AC
Brushless motor, 301, 303
Buck-boost converter, 110
Buck converter, 108 - 109
Burst firing, 537
Burst pulses, 564

Capacitance
  junction, 29
Capacitor
  mains dropper, 544
CENELEC, 537
Charge carriers, 133
  triac commutation, 549
Choke
  fluorescent lamp, 580
Choppers, 285
Clamp diode, 117
Clamp winding, 113
Commutation
  diode, 164
  Hi-Com triac, 551
  thyristor, 492
  triac, 494, 523, 529
Compact fluorescent lamp, 585
Continuous mode
  see Switched Mode Power Supplies
Continuous operation, 557
Converter (dc-dc)
  switched mode power supply, 107
Cookers, 537
Cooling
  forced, 572
  natural, 570
Crest factor, 529
Critical electric field, 134
Cross regulation, 114, 117
Current fed resonant inverter, 589
Current Mode Control, 120
Current tail, 138, 143

Damper Diodes, 345, 367
  forward recovery, 328, 348
  losses, 347
  outlines, 345
  picture distortion, 328, 348
  selection guide, 345
Darlington, 13
Data Sheets
  High Voltage Bipolar Transistor, 92,97,331
  MOSFET, 69

dc-dc converter, 119
Depletion region, 133
Desaturation networks, 86
  Baker clamp, 91, 138
dI/dt
  triac, 531
Diac, 492, 500, 527, 530, 591
Diode, 6
  double diffused, 162
  epitaxial, 161
  schottky, 173
  structure, 161
Diode Modulator, 327, 367
Disc drives, 302
Discontinuous mode
  see Switched Mode Power Supplies
Domestic Appliances, 527
Dropper
  capacitive, 544
  resistive, 544, 545
Duty cycle, 561

EFD core
  see magnetics
Efficiency Diodes
  see Damper Diodes
Electric drill, 531
Electronic ballast, 580
  base drive optimisation, 589
  current fed half bridge, 584, 587, 589
  current fed push pull, 583, 587
  flyback, 582
  transistor selection guide, 587
  voltage fed half bridge, 584, 588
  voltage fed push pull, 583, 587
EMC, 260, 455
  see RFI, ESD
  TOPFET, 473
Emitter shorting
  triac, 549
Epitaxial diode, 161
  characteristics, 163
  dI/dt, 164
  forward recovery, 168
  lifetime control, 162
  operating frequency, 165
  passivation, 162
  reverse leakage, 169
  reverse recovery, 162, 164
  reverse recovery softness, 167
  selection guide, 171
  snap-off, 167
  softness factor, 167
  stored charge, 162
  technology, 162
ESD, 67
  see Protection, ESD
  precautions, 67
ETD core
  see magnetics

F-pack
  see isolated package
Fall time, 143, 144
Fast Recovery Epitaxial Diode (FRED)
  see epitaxial diode
FBSOA, 134
Ferrites
  see magnetics
Flicker
  fluorescent lamp, 580
Fluorescent lamp, 579
  colour rendering, 579
  colour temperature, 579
  efficacy, 579, 580
  triphosphor, 579
Flyback converter, 110, 111, 113
  advantages, 114
  clamp winding, 113
  continuous mode, 114
  coupled inductor, 113
  cross regulation, 114
  diodes, 115
  disadvantages, 114
  discontinuous mode, 114
  electronic ballast, 582
  leakage inductance, 113
  magnetics, 213
  operation, 113
  rectifier circuit, 180
  self oscillating power supply, 199
  synchronous rectifier, 156, 181
  transformer core airgap, 111, 113
  transistors, 115
Flyback converter (two transistor), 111, 114
Food mixer, 531
Forward converter, 111, 116
  advantages, 116
  clamp diode, 117
  conduction loss, 197
  continuous mode, 116
  core loss, 116
  core saturation, 117
  cross regulation, 117
  diodes, 118
  disadvantages, 117
  duty ratio, 117
  ferrite cores, 116
  magnetics, 213
  magnetisation energy, 116, 117

operation, 116
output diodes, 117
output ripple, 116
rectifier circuit, 180
reset winding, 117
switched mode power supply, 187
switching frequency, 195
switching losses, 196
synchronous rectifier, 157, 181
transistors, 118
Forward converter (two transistor), 111, 117
Forward recovery, 168
FREDFET, 250, 253, 305
bridge circuit, 255
charge, 254
diode, 254
drive, 262
loss, 256
reverse recovery, 254
FREDFETs
motor control, 259
Full bridge converter, 111, 125
advantages, 125
diodes, 126
disadvantages, 125
operation, 125
transistors, 126

Gate
triac, 538
Gate drive
forward converter, 195
Gold doping, 162, 169
GTO, 11
Guard ring
schottky diode, 174

Half bridge, 253
Half bridge circuits
see also Motor Control - AC
Half bridge converter, 111, 122
advantages, 122
clamp diodes, 122
cross conduction, 122
diodes, 124
disadvantages, 122
electronic ballast, 584, 587, 589
flux symmetry, 122
magnetics, 214
operation, 122
synchronous rectifier, 157
transistor voltage, 122
transistors, 124
voltage doubling, 122
Heat dissipation, 567
Heat sink compound, 567
Heater controller, 544
Heaters, 537
Heatsink, 569
Heatsink compound, 514
Hi-Com triac, 519, 549, 551
commutation, 551
dIcom/dt, 552
gate trigger current, 552
inductive load control, 551
High side switch
MOSFET, 44, 436
TOPFET, 430, 473
High Voltage Bipolar Transistor, 8, 79, 91, 141, 341
‘bathtub’ curves, 333
avalanche breakdown, 131
avalanche multiplication, 134
Baker clamp, 91, 138
base-emitter breakdown, 144
base drive, 83, 92, 96, 136, 336, 385
base drive circuit, 145
base inductor, 138, 144, 147
base inductor, diode assisted, 148
base resistor, 146
breakdown voltage, 79, 86, 92
carrier concentration, 151
carrier injection, 150
conductivity modulation, 135, 150
critical electric field, 134
current crowding, 135, 136
current limiting values, 132
current tail, 138, 143
current tails, 86, 91
d-type, 346
data sheet, 92, 97, 331
depletion region, 133
desaturation, 86, 88, 91
device construction, 79
dI/dt, 139
drive transformer, 145
drive transformer leakage inductance, 149
dV/dt, 139
electric field, 133
electronic ballast, 581, 585, 587, 589
Fact Sheets, 334
fall time, 86, 99, 143, 144
FBSOA, 92, 99, 134
hard turn-off, 86
horizontal deflection, 321, 331, 341
leakage current, 98
limiting values, 97
losses, 92, 333, 342
Miller capacitance, 139
operation, 150

optimum drive, 88
outlines, 332, 346
over current, 92, 98
over voltage, 92, 97
overdrive, 85, 88, 137, 138
passivation, 131
power limiting value, 132
process technology, 80
ratings, 97
RBSOA, 93, 99, 135, 138, 139
RC network, 148
reverse recovery, 143, 151
safe operating area, 99, 134
saturation, 150
saturation current, 79, 98, 341
secondary breakdown, 92, 133
smooth turn-off, 86
SMPS, 94, 339, 383
snubber, 139
space charge, 133
speed-up capacitor, 143
storage time, 86, 91, 92, 99, 138, 144, 342
sub emitter resistance, 135
switching, 80, 83, 86, 91, 98, 342
technology, 129, 149
thermal breakdown, 134
thermal runaway, 152
turn-off, 91, 92, 138, 142, 146, 151
turn-on, 91, 136, 141, 149, 150
underdrive, 85, 88
voltage limiting values, 130
Horizontal Deflection, 321, 367
base drive, 336
control ic, 401
d-type transistors, 346
damper diodes, 345, 367
diode modulator, 327, 347, 352, 367
drive circuit, 352, 365, 406
east-west correction, 325, 352, 367
line output transformer, 354
linearity correction, 323
operating cycle, 321, 332, 347
s-correction, 323, 352, 404
TDA2595, 364, 368
TDA4851, 400
TDA8433, 363, 369
test circuit, 321
transistors, 331, 341, 408
waveforms, 322

IGBT, 11, 305
automotive, 481, 483
clamped, 482, 484
ignition, 481, 483

Ignition
automotive, 479, 481, 483
darlington, 483
Induction heating, 53
Induction motor
see Motor Control - AC
Inductive load
see Solenoid
Inrush current, 528, 530
Intrinsic silicon, 133
Inverter, 260, 273
see motor control ac
current fed, 52, 53
switched mode power supply, 107
Irons, electric, 537
Isolated package, 154
stray capacitance, 154, 155
thermal resistance, 154
Isolation, 153

J-FET, 9
Junction temperature, 470, 557, 561
burst pulses, 564
non-rectangular pulse, 565
rectangular pulse, composite, 562
rectangular pulse, periodic, 561
rectangular pulse, single shot, 561

Lamp dimmer, 530
Lamps, 435
dI/dt, 438
inrush current, 438
MOSFET, 435
PWM control, 455
switch rate, 438
TOPFET, 455
Latching current
thyristor, 490
Leakage inductance, 113, 200, 523
Lifetime control, 162
Lighting
fluorescent, 579
phase control, 530
Logic Level FET
motor control, 432
Logic level MOSFET, 436

Magnetics, 207
100W 100kHz forward converter, 197
100W 50kHz forward converter, 191
50W flyback converter, 199
core losses, 208
core materials, 207
EFD core, 210
ETD core, 199, 207

flyback converter, 213
forward converter, 213
half bridge converter, 214
power density, 211
push-pull converter, 213
switched mode power supply, 187
switching frequency, 215
transformer construction, 215
Mains Flicker, 537
Mains pollution, 225
pre-converter, 225
Mains transient, 544
Mesa glass, 162
Metal Oxide Varistor (MOV), 503
Miller capacitance, 139
Modelling, 236, 265
MOS Controlled Thyristor, 13
MOSFET, 9, 19, 153, 253
bootstrap, 303
breakdown voltage, 22, 70
capacitance, 30, 57, 72, 155, 156
capacitances, 24
characteristics, 23, 70 - 72
charge, 32, 57
data sheet, 69
dI/dt, 36
diode, 253
drive, 262, 264
drive circuit loss, 156
driving, 39, 250
dV/dt, 36, 39, 264
ESD, 67
gate-source protection, 264
gate charge, 195
gate drive, 195
gate resistor, 156
high side, 436
high side drive, 44
inductive load, 62
lamps, 435
leakage current, 71
linear mode, parallelling, 52
logic level, 37, 57, 305
loss, 26, 34
maximum current, 69
motor control, 259, 429
modelling, 265
on-resistance, 21, 71
package inductance, 49, 73
parallel operation, 26, 47, 49, 265
parasitic oscillations, 51
peak current rating, 251
Resonant supply, 53
reverse diode, 73
ruggedness, 61, 73
safe operating area, 25, 74
series operation, 53
SMPS, 339, 384
solenoid, 62
structure, 19
switching, 24, 29, 58, 73, 194, 262
switching loss, 196
synchronous rectifier, 179
thermal impedance, 74
thermal resistance, 70
threshold voltage, 21, 70
transconductance, 57, 72
turn-off, 34, 36
turn-on, 32, 34, 35, 155, 256
Motor, universal
back EMF, 531
starting, 528
Motor Control - AC, 245, 273
anti-parallel diode, 253
antiparallel diode, 250
carrier frequency, 245
control, 248
current rating, 262
dc link, 249
diode, 261
diode recovery, 250
duty ratio, 246
efficiency, 262
EMC, 260
filter, 250
FREDFET, 250, 259, 276
gate drives, 249
half bridge, 245
inverter, 250, 260, 273
line voltage, 262
loss, 267
MOSFET, 259
Parallel MOSFETs, 276
peak current, 251
phase voltage, 262
power factor, 262
pulse width modulation, 245, 260
ripple, 246
short circuit, 251
signal isolation, 250
snubber, 276
speed control, 248
switching frequency, 246
three phase bridge, 246
underlap, 248
Motor Control - DC, 285, 293, 425
braking, 285, 299
brushless, 301
control, 290, 295, 303
current rating, 288

drive, 303
duty cycle, 286
efficiency, 293
FREDFET, 287
freewheel diode, 286
full bridge, 287
half bridge, 287
high side switch, 429
IGBT, 305
inrush, 430
inverter, 302
linear, 457, 475
logic level FET, 432
loss, 288
MOSFET, 287, 429
motor current, 295
overload, 430
permanent magnet, 293, 301
permanent magnet motor, 285
PWM, 286, 293, 459, 471
servo, 298
short circuit, 431
stall, 431
TOPFET, 430, 457, 459, 475
topologies, 286
torque, 285, 294
triac, 525
voltage rating, 288
Motor Control - Stepper, 309
bipolar, 310
chopper, 314
drive, 313
hybrid, 312
permanent magnet, 309
reluctance, 311
step angle, 309
unipolar, 310
Mounting, transistor, 154
Mounting base temperature, 557
Mounting torque, 514

Parasitic oscillation, 149
Passivation, 131, 162
PCB Design, 368, 419
Phase angle, 500
Phase control, 546
thyristors and triacs, 498
triac, 523
Phase voltage
see motor control - ac
Power dissipation, 557
see High Voltage Bipolar Transistor loss, MOSFET loss
Power factor correction, 580
active, boost converted, 581
Power MOSFET
see MOSFET
Proportional control, 537
Protection
ESD, 446, 448, 482
overvoltage, 446, 448, 469
reverse battery, 452, 473, 479
short circuit, 251, 446, 448
temperature, 446, 447, 471
TOPFET, 445, 447, 451
Pulse operation, 558
Pulse Width Modulation (PWM), 108
Push-pull converter, 111, 119
advantages, 119
clamp diodes, 119
cross conduction, 119
current mode control, 120
diodes, 121
disadvantages, 119
duty ratio, 119
electronic ballast, 582, 587
flux symmetry, 119, 120
magnetics, 213
multiple outputs, 119
operation, 119
output filter, 119
output ripple, 119
rectifier circuit, 180
switching frequency, 119
transformer, 119
transistor voltage, 119
transistors, 121

Qs (stored charge), 162

RBSOA, 93, 99, 135, 138, 139
Rectification, synchronous, 179
Reset winding, 117
Resistor
mains dropper, 544, 545
Resonant power supply, 219, 225
modelling, 236
MOSFET, 52, 53
pre-converter, 225
Reverse leakage, 169
Reverse recovery, 143, 162
RFI, 154, 158, 167, 393, 396, 497, 529, 530, 537
Ruggedness
MOSFET, 62, 73
schottky diode, 173

Safe Operating Area (SOA), 25, 74, 134, 557
forward biased, 92, 99, 134
reverse biased, 93, 99, 135, 138, 139

Saturable choke
  triac, 523
Schottky diode, 173
  bulk leakage, 174
  edge leakage, 174
  guard ring, 174
  reverse leakage, 174
  ruggedness, 173
  selection guide, 176
  technology, 173
SCR
  see Thyristor
Secondary breakdown, 133
Selection Guides
  BU25XXA, 331
  BU25XXD, 331
  damper diodes, 345
  EPI diodes, 171
  horizontal deflection, 343
  MOSFETs driving heaters, 442
  MOSFETs driving lamps, 441
  MOSFETs driving motors, 426
  Schottky diodes, 176
  SMPS, 339
Self Oscillating Power Supply (SOPS)
  50W microcomputer flyback converter, 199
  ETD transformer, 199
Servo, 298
Single ended push-pull
  see half bridge converter
Snap-off, 167
Snubber, 93, 139, 495, 502, 523, 529, 549
  active, 279
Softness factor, 167
Solenoid
  TOPFET, 469, 473
  turn off, 469, 473
Solid state relay, 501
SOT186, 154
SOT186A, 154
SOT199, 154
Space charge, 133
Speed-up capacitor, 143
Speed control
  thyristor, 531
  triac, 527
Starter
  fluorescent lamp, 580
Startup circuit
  electronic ballast, 591
  self oscillating power supply, 201
Static Induction Thyristor, 11
Stepdown converter, 109
Stepper motor, 309
Stepup converter, 109
Storage time, 144
Stored charge, 162
Suppression
  mains transient, 544
Switched Mode Power Supply (SMPS)
  see also self oscillating power supply
  100W 100kHz MOSFET forward converter, 192
  100W 500kHz half bridge converter, 153
  100W 50kHz bipolar forward converter, 187
  16 & 32 kHz TV, 389
  asymmetrical, 111, 113
  base circuit design, 149
  boost converter, 109
  buck-boost converter, 110
  buck converter, 108
  ceramic output filter, 153
  continuous mode, 109, 379
  control ic, 391
  control loop, 108
  core excitation, 113
  core loss, 167
  current mode control, 120
  dc-dc converter, 119
  diode loss, 166
  diode reverse recovery effects, 166
  diode reverse recovery softness, 167
  diodes, 115, 118, 121, 124, 126
  discontinuous mode, 109, 379
  epitaxial diodes, 112, 161
  flux swing, 111
  flyback converter, 92, 111, 113, 123
  forward converter, 111, 116, 379
  full bridge converter, 111, 125
  half bridge converter, 111, 122
  high voltage bipolar transistor, 94, 112, 115, 118, 121, 124, 126, 129, 339, 383, 392
  isolated, 113
  isolated packages, 153
  isolation, 108, 111
  magnetics design, 191, 197
  magnetisation energy, 113
  mains filter, 380
  mains input, 390
  MOSFET, 112, 153, 33, 384
  multiple output, 111, 156
  non-isolated, 108
  opto-coupler, 392
  output rectifiers, 163
  parasitic oscillation, 149
  power-down, 136
  power-up, 136, 137, 139
  power MOSFET, 153, 339, 384
  pulse width modulation, 108
  push-pull converter, 111, 119

RBSOA failure, 139
rectification, 381, 392
rectification efficiency, 163
rectifier selection, 112
regulation, 108
reliability, 139
resonant
see resonant power supply
RFI, 154, 158, 167
schottky diode, 112, 154, 173
snubber, 93, 139, 383
soft start, 138
standby, 382
standby supply, 392
start-up, 391
stepdown, 109
stepup, 109
symmetrical, 111, 119, 122
synchronisation, 382
synchronous rectification, 156, 179
TDA8380, 381, 391
topologies, 107
topology output powers, 111
transformer, 111
transformer saturation, 138
transformers, 391
transistor current limiting value, 112
transistor mounting, 154
transistor selection, 112
transistor turn-off, 138
transistor turn-on, 136
transistor voltage limiting value, 112
transistors, 115, 118, 121, 124, 126
turns ratio, 111
TV & Monitors, 339, 379, 399
two transistor flyback, 111, 114
two transistor forward, 111, 117
Switching loss, 230
Synchronous, 497
Synchronous rectification, 156, 179
self driven, 181
transformer driven, 180

Temperature control, 537
Thermal
continuous operation, 557, 568
intermittent operation, 568
non-rectangular pulse, 565
pulse operation, 558
rectangular pulse, composite, 562
rectangular pulse, periodic, 561
rectangular pulse, single shot, 561
single shot operation, 561
Thermal capacity, 558, 568
Thermal characteristics
power semiconductors, 557
Thermal impedance, 74, 568
Thermal resistance, 70, 154, 557
Thermal time constant, 568
Thyristor, 10, 497, 509
'two transistor' model, 490
applications, 527
asynchronous control, 497
avalanche breakdown, 490
breakover voltage, 490, 509
cascading, 501
commutation, 492
control, 497
current rating, 511
dI/dt, 490
dIf/dt, 491
dV/dt, 490
energy handling, 505
external commutation, 493
full wave control, 499
fusing I^2t, 503, 512
gate cathode resistor, 500
gate circuits, 500
gate current, 490
gate power, 492
gate requirements, 492
gate specifications, 512
gate triggering, 490
half wave control, 499
holding current, 490, 509
inductive loads, 500
inrush current, 503
latching current, 490, 509
leakage current, 490
load line, 492
mounting, 514
operation, 490
overcurrent, 503
peak current, 505
phase angle, 500
phase control, 498, 527
pulsed gate, 500
resistive loads, 498
resonant circuit, 493
reverse characteristic, 489
reverse recovery, 493
RFI, 497
self commutation, 493
series choke, 502
snubber, 502
speed controller, 531
static switching, 497
structure, 489
switching, 489

switching characteristics, 517
synchronous control, 497
temperature rating, 512
thermal specifications, 512
time proportional control, 497
transient protection, 502
trigger angle, 500
turn-off time, 494
turn-on, 490, 509
turn-on dI/dt, 502
varistor, 503
voltage rating, 510
Thyristor data, 509
Time proportional control, 537
TOPFET
3 pin, 445, 449, 461
5 pin, 447, 451, 457, 459, 463
driving, 449, 453, 461, 465, 467, 475
high side, 473, 475
lamps, 455
leadforms, 463
linear control, 451, 457
motor control, 430, 457, 459
negative input, 456, 465, 467
protection, 445, 447, 451, 469, 473
PWM control, 451, 455, 459
solenoids, 469
Transformer
triac controlled, 523
Transformer core airgap, 111, 113
Transformers
see magnetics
Transient thermal impedance, 559
Transient thermal response, 154
Triac, 497, 510, 518
400Hz operation, 489, 518
applications, 527, 537
asynchronous control, 497
breakover voltage, 510
charge carriers, 549
commutating dI/dt, 494
commutating dV/dt, 494
commutation, 494, 518, 523, 529, 549
control, 497
dc inductive load, 523
dc motor control, 525
dI/dt, 531, 549
dIcom/dt, 523
dV/dt, 523, 549
emitter shorting, 549
full wave control, 499
fusing I^2t, 503, 512
gate cathode resistor, 500
gate circuits, 500
gate current, 491
gate requirements, 492
gate resistor, 540, 545
gate sensitivity, 491
gate triggering, 538
holding current, 491, 510
Hi-Com, 549, 551
inductive loads, 500
inrush current, 503
isolated trigger, 501
latching current, 491, 510
operation, 491
overcurrent, 503
phase angle, 500
phase control, 498, 527, 546
protection, 544
pulse triggering, 492
pulsed gate, 500
quadrants, 491, 510
resistive loads, 498
RFI, 497
saturable choke, 523
series choke, 502
snubber, 495, 502, 523, 529, 549
speed controller, 527
static switching, 497
structure, 489
switching, 489
synchronous control, 497
transformer load, 523
transient protection, 502
trigger angle, 492, 500
triggering, 550
turn-on dI/dt, 502
varistor, 503
zero crossing, 537
Trigger angle, 500
TV & Monitors
16 kHz black line, 351
30-64 kHz autosync, 399
32 kHz black line, 361
damper diodes, 345, 367
diode modulator, 327, 367
EHT, 352 - 354, 368, 409, 410
high voltage bipolar transistor, 339, 341
horizontal deflection, 341
picture distortion, 348
power MOSFET, 339
SMPS, 339, 354, 379, 389, 399
vertical deflection, 358, 364, 402
Two transistor flyback converter, 111, 114
Two transistor forward converter, 111, 117

Universal motor
back EMF, 531

starting, 528

Vacuum cleaner, 527
Varistor, 503
Vertical Deflection, 358, 364, 402
Voltage doubling, 122

Water heaters, 537

Zero crossing, 537
Zero voltage switching, 537